

**AUTOMOTIVE, 125°C OPERATION,
36 V INPUT, 40 mA VOLTAGE REGULATOR
WITH SENSE-INPUT RESET FUNCTION**

The S-19315 Series, developed by using high-withstand voltage CMOS process technology, is a positive voltage regulator with the reset function, which has high-withstand voltage and low current consumption.

Apart from the power supply pin, the detection voltage input pin (SENSE pin) is also prepared for the reset function, so the output is stable even if the SENSE pin falls to 0 V. The output form is Nch open-drain output.

ABLIC Inc. offers a "thermal simulation service" which supports the thermal design in conditions when our power management ICs are in use by customers. Our thermal simulation service will contribute to reducing the risk in the thermal design at customers' development stage.

ABLIC Inc. also offers FIT rate calculated based on actual customer usage conditions in order to support customer functional safety design.

Contact our sales representatives for details.

Caution This product can be used in vehicle equipment and in-vehicle equipment. Before using the product for these purposes, it is imperative to contact our sales representatives.

■ Features

Regulator block

- Output voltage: 1.0 V to 5.3 V, selectable in 0.1 V step
- Input voltage: 3.0 V to 36.0 V
- Output voltage accuracy: ± 0.03 V ($1.0 \text{ V} \leq V_{\text{OUT(S)}} < 1.5 \text{ V}$, $T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$)
 $\pm 2.0\%$ ($1.5 \text{ V} \leq V_{\text{OUT(S)}} \leq 5.3 \text{ V}$, $T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$)
- Dropout voltage: 240 mV typ. ($V_{\text{OUT(S)}} = 5.0 \text{ V}$, $I_{\text{OUT}} = 30 \text{ mA}$)
- Output current: Possible to output 40 mA ($1.0 \text{ V} \leq V_{\text{OUT(S)}} < 2.0 \text{ V}$, $V_{\text{IN}} = 4.0 \text{ V}$)*¹
Possible to output 40 mA ($2.0 \text{ V} \leq V_{\text{OUT(S)}} \leq 5.3 \text{ V}$, $V_{\text{IN}} = V_{\text{OUT(S)}} + 2.0 \text{ V}$)*¹
- Input and output capacitors: A ceramic capacitor can be used. (1.0 μF or more)
- Built-in overcurrent protection circuit: Limits overcurrent of output transistor
- Built-in thermal shutdown circuit: Detection temperature 160°C typ.
- Built-in discharge shunt circuit: Discharges output capacitor electrical charge during detector detection

Detector block

- Detection voltage: 3.0 V to 11.3 V, selectable in 0.1 V step
- Operation voltage: 3.0 V to 36.0 V
- Detection voltage accuracy: $\pm 2.0\%$ ($T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$)
- Hysteresis width selectable from "Available": $5.0\% \leq V_{\text{HYS}} \leq 30.0\%$ ($T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$)
"Unavailable": $V_{\text{HYS}} = 0\%$
- Output form: Nch open-drain output

Overall

- Current consumption: During operation: 2.0 μA typ. ($T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$)
During detector detection: 0.5 μA typ. ($T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$)
- Operation temperature range: $T_a = -40^\circ\text{C}$ to $+125^\circ\text{C}$
- Lead-free (Sn 100%), halogen-free
- Withstand 45 V load dump
- AEC-Q100 qualified*²

*1. Please make sure that the loss of the IC will not exceed the power dissipation when the output current is large.

*2. Contact our sales representatives for details.

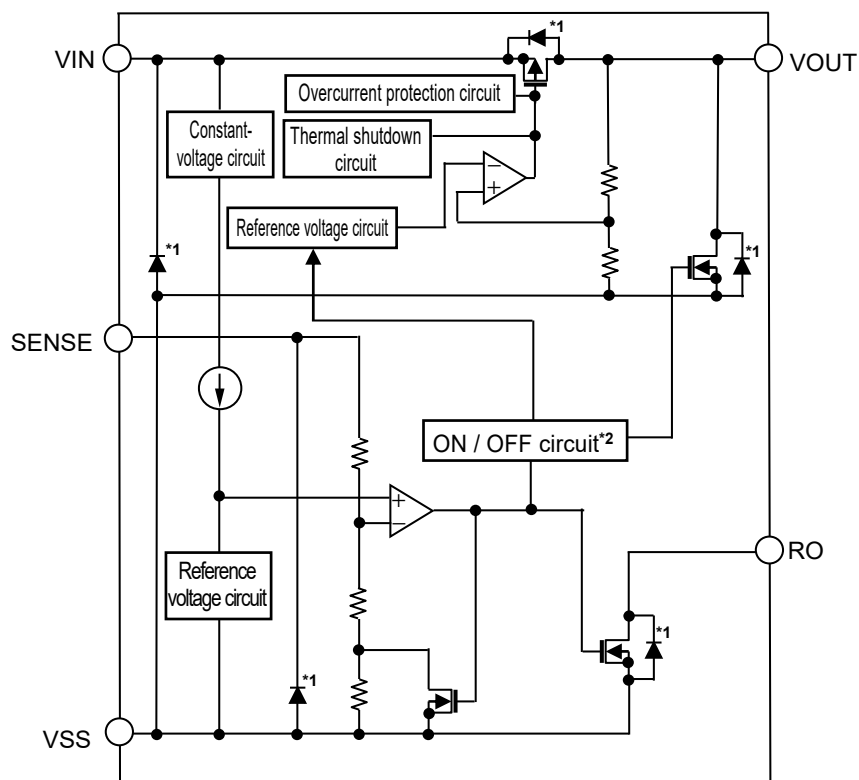
■ Applications

- Constant-voltage power supply and reset circuit for automotive electric component
- Power supply and reset circuit for low-current battery-powered device

■ Packages

- SOT-89-5
- HTMSOP-8
- SOT-23-5

■ Block Diagram



*1. Parasitic diode

*2. The ON / OFF circuit controls the internal circuit of the regulator and the output transistor.

Figure 1

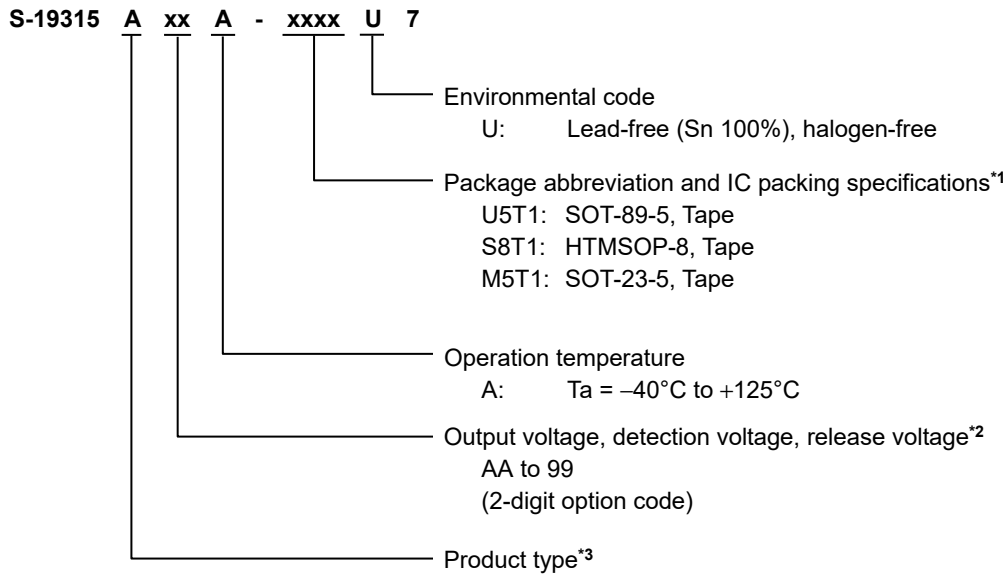
■ **AEC-Q100 Qualified**

This IC supports AEC-Q100 for operation temperature grade 1.
 Contact our sales representatives for details of AEC-Q100 reliability specification.

■ **Product Name Structure**

Users can select the output voltage, detection voltage, release voltage, and package type for the S-19315 Series. Refer to "1. **Product name**" regarding the contents of product name, "3. **Packages**" regarding the package drawings.

1. **Product name**



- *1. Refer to the tape drawing.
- *2. Contact our sales representatives for details on combination of output voltage, detection voltage, and release voltage.
- *3. Refer to "2. **Function list of product type**".

- Remark 1.** The output voltage (V_{OUT}) can be set in a range which satisfies the following conditions.
- Set output voltage ($V_{OUT(S)}$) is 100 mV step
 - $1.0\text{ V} \leq V_{OUT(S)} \leq 5.3\text{ V}$
- 2.** The detection voltage ($-V_{DET}$) can be set in a range which satisfies the following conditions.
- Set detection voltage ($-V_{DET(S)}$) is 100 mV step
 - $3.0\text{ V} \leq -V_{DET(S)} \leq 11.3\text{ V}$
- 3.** The release voltage ($+V_{DET}$) can be set in a range which satisfies the following conditions.
 Release voltage possible setting range is shown in **Figure 2**.
- Set release voltage ($+V_{DET(S)}$) is 100 mV step
 - $5.0\% \leq V_{HYS} \leq 30.0\%$

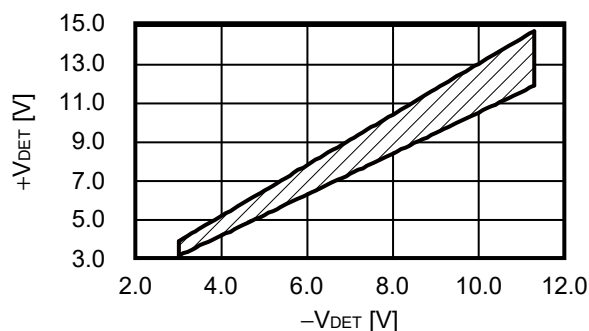


Figure 2 Release Voltage Possible Setting Area

If hysteresis width "Unavailable" was selected, $+V_{DET} = -V_{DET}$.

2. Function list of product type

Table 1

Product Type	RO Pin Output Form	RO Pin Output Logic
A	Nch open-drain output	Active "L"

3. Packages

Table 2 Package Drawing Codes

Package Name	Dimension	Tape	Reel	Land
SOT-89-5	UP005-A-P-SD	UP005-A-C-SD	UP005-A-R-SD	-
HTMSOP-8	FP008-A-P-SD	FP008-A-C-SD	FP008-A-R-SD	FP008-A-L-SD
SOT-23-5	MP005-A-P-SD	MP005-A-C-SD	MP005-A-R-SD	-

Pin Configurations

1. SOT-89-5

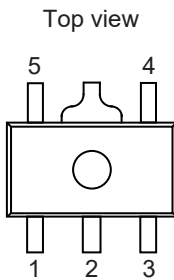


Figure 3

Table 3

Pin No.	Symbol	Description
1	SENSE	Detection voltage input pin
2	VSS	GND pin
3	VIN	Input voltage pin
4	VOUT	Output voltage pin
5	RO	Reset output pin

2. HTMSOP-8

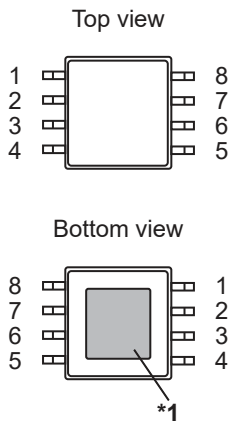


Figure 4

Table 4

Pin No.	Symbol	Description
1	NC*2	No connection
2	VOUT	Output voltage pin
3	RO	Reset output pin
4	NC*2	No connection
5	SENSE	Detection voltage input pin
6	VSS	GND pin
7	NC*2	No connection
8	VIN	Input voltage pin

*1. Connect the heat sink of backside at shadowed area to the board, and set electric potential GND. However, do not use it as the function of electrode.

*2. The NC pin is electrically open.
 The NC pin can be connected to the VIN pin or the VSS pin.

3. SOT-23-5

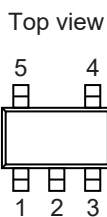


Figure 5

Table 5

Pin No.	Symbol	Description
1	RO	Reset output pin
2	VSS	GND pin
3	VOUT	Output voltage pin
4	VIN	Input voltage pin
5	SENSE	Detection voltage input pin

■ **Absolute Maximum Ratings**

Table 6

(Ta = +25°C unless otherwise specified)

Item	Symbol	Absolute Maximum Rating	Unit
Input voltage	V _{IN}	V _{SS} – 0.3 to V _{SS} + 45.0	V
Output voltage	V _{OUT}	V _{SS} – 0.3 to V _{IN} + 0.3 ≤ V _{SS} + 7.0	V
RO pin voltage	V _{RO}	V _{SS} – 0.3 to V _{SS} + 45.0	V
SENSE pin voltage	V _{SENSE}	V _{SS} – 0.3 to V _{SS} + 45.0	V
Output current (Regulator block)	I _{OUT}	52	mA
Output current (Detector block)	I _{RON}	20	mA
Junction temperature	T _j	–40 to +150	°C
Operation ambient temperature	T _{opr}	–40 to +125	°C
Storage temperature	T _{stg}	–40 to +150	°C

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ **Thermal Resistance Value**

Table 7

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	
Junction-to-ambient thermal resistance*1	θ _{JA}	SOT-89-5	Board A	–	119	–	°C/W
			Board B	–	84	–	°C/W
			Board C	–	–	–	°C/W
			Board D	–	46	–	°C/W
			Board E	–	35	–	°C/W
		HTMSOP-8	Board A	–	159	–	°C/W
			Board B	–	113	–	°C/W
			Board C	–	39	–	°C/W
			Board D	–	40	–	°C/W
			Board E	–	30	–	°C/W
		SOT-23-5	Board A	–	192	–	°C/W
			Board B	–	160	–	°C/W
			Board C	–	–	–	°C/W
			Board D	–	–	–	°C/W
			Board E	–	–	–	°C/W

*1. Test environment: compliance with JEDEC STANDARD JESD51-2A

Remark Refer to "■ Power Dissipation" and "Test Board" for details.

■ Electrical Characteristics

1. Regulator block

Table 8
 (V_{SENSE} = 16.0 V, T_J = -40°C to +125°C unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit	
Output voltage*1	V _{OUT(E)}	V _{IN} = V _{OUT(S)} + 2.0 V, I _{OUT} = 1 mA	1.0 V ≤ V _{OUT(S)} < 1.5 V	V _{OUT(S)} - 0.03	V _{OUT(S)}	V _{OUT(S)} + 0.03	V	1
			1.5 V ≤ V _{OUT(S)} ≤ 5.3 V	V _{OUT(S)} × 0.98	V _{OUT(S)}	V _{OUT(S)} × 1.02	V	1
Output current*2	I _{OUT}	V _{IN} = 4.0 V	1.0 V ≤ V _{OUT(S)} < 2.0 V	40*4	-	-	mA	2
		V _{IN} = V _{OUT(S)} + 2.0 V	2.0 V ≤ V _{OUT(S)} ≤ 5.3 V	40*4	-	-	mA	2
Dropout voltage*3	V _{drop}	I _{OUT} = 30 mA	1.0 V ≤ V _{OUT(S)} < 1.5 V	2.00	2.19	2.38	V	1
			1.5 V ≤ V _{OUT(S)} < 2.0 V	1.50	1.73	1.95	V	1
			2.0 V ≤ V _{OUT(S)} < 2.5 V	1.00	1.19	1.39	V	1
			2.5 V ≤ V _{OUT(S)} < 3.0 V	0.50	0.66	0.82	V	1
			3.0 V ≤ V _{OUT(S)} < 4.0 V	-	0.35	0.60	V	1
4.0 V ≤ V _{OUT(S)} ≤ 5.3 V	-	0.24	0.45	V	1			
Line regulation	$\frac{\Delta V_{OUT1}}{\Delta V_{IN} \cdot V_{OUT}}$	V _{OUT(S)} + 2.0 V ≤ V _{IN} ≤ 36.0 V, I _{OUT} = 1 mA	-	0.01	0.2	%/V	1	
Load regulation	ΔV _{OUT2}	V _{IN} = 4.0 V, 1 μA ≤ I _{OUT} ≤ 30 mA	1.0 V ≤ V _{OUT(S)} < 2.0 V	-	24	45	mV	1
		V _{IN} = V _{OUT(S)} + 2.0 V, 1 μA ≤ I _{OUT} ≤ 30 mA	2.0 V ≤ V _{OUT(S)} ≤ 5.3 V	-	24	45	mV	1
Input voltage	V _{IN}	-	3.0	-	36.0	V	-	
Short-circuit current	I _{short}	V _{IN} = 4.0 V, V _{OUT} = 0 V	1.0 V ≤ V _{OUT(S)} < 2.0 V	-	24	-	mA	2
		V _{IN} = V _{OUT(S)} + 2.0 V, V _{OUT} = 0 V	2.0 V ≤ V _{OUT(S)} ≤ 5.3 V	-	24	-	mA	2
Thermal shutdown detection temperature	T _{SD}	Junction temperature	-	160	-	°C	-	
Thermal shutdown release temperature	T _{SR}	Junction temperature	-	135	-	°C	-	
Discharge shunt resistance during power-off	R _{LOW}	V _{IN} = 16.0 V, V _{SENSE} = 0.0 V, V _{OUT} = 0.1 V	-	0.65	-	kΩ	6	

- *1. V_{OUT(S)}: Set output voltage
 V_{OUT(E)}: Actual output voltage
 Output voltage when fixing I_{OUT} (= 1 mA) and inputting V_{OUT(S)} + 2.0 V
- *2. The output current at which the output voltage becomes 95% of V_{OUT(E)} after gradually increasing the output current.
- *3. V_{drop} = V_{IN1} - (V_{OUT3} × 0.98)
 V_{IN1} is the input voltage at which the output voltage becomes 98% of V_{OUT3} after gradually decreasing the input voltage.
 V_{OUT3} is the output voltage when V_{IN} = 4.0 V (1.0 V ≤ V_{OUT(S)} < 2.0 V), or V_{IN} = V_{OUT(S)} + 2.0 V (2.0 V ≤ V_{OUT(S)} ≤ 5.3 V), and I_{OUT} = 30 mA
- *4. Due to limitation of the power dissipation, this value may not be satisfied. Attention should be paid to the power dissipation when the output current is large.
 This specification is guaranteed by design.

2. Detector block

Table 9

($V_{IN} = 16.0\text{ V}$, $T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Detection voltage*1	$-V_{DET}$	–	$-V_{DET(S)} \times 0.98$	$-V_{DET(S)}$	$-V_{DET(S)} \times 1.02$	V	3
Release voltage*2	$+V_{DET}$	$V_{HYS} = 0\%$	$-V_{DET(S)} \times 0.98$	$-V_{DET(S)}$	$-V_{DET(S)} \times 1.02$	V	3
		$5.0\% \leq V_{HYS} \leq 30.0\%$	$+V_{DET(S)} \times 0.98$	$+V_{DET(S)}$	$+V_{DET(S)} \times 1.02$	V	3
Operation voltage	V_{OPR}	–	3.0	–	36.0	V	–
Output current "L"	I_{RON}	Nch open-drain output	3.00	–	–	mA	4
Leakage current	I_{LEAKN}						
		$V_{RO} = 36.0\text{ V}$, $V_{IN} = 36.0\text{ V}$, $V_{SENSE} = 16.0\text{ V}$	–	–	2.0	μA	4
Detection response time*4	t_{RESET}	$V_{IN} = 3.0\text{ V}$	–	65	–	μs	5
Release response time*5	t_{DELAY}	$V_{IN} = 3.0\text{ V}$	–	80	–	μs	5
SENSE pin resistance	R_{SENSE}	–	13	–	–	$\text{M}\Omega$	7

*1. $-V_{DET(S)}$: Set detection voltage, $-V_{DET}$: Actual detection voltage

*2. $+V_{DET(S)}$: Set release voltage, $+V_{DET}$: Actual release voltage

*3. V_{DS} : Drain-to-source voltage of the output transistor

*4. The time period from when the pulse voltage of $-V_{DET(S)} + 1.0\text{ V} \rightarrow -V_{DET(S)} - 1.0\text{ V}$ is applied to the SENSE pin to when V_{RO} reaches 50% of V_{IN} .

*5. The time period from when the pulse voltage of $+V_{DET(S)} - 1.0\text{ V} \rightarrow +V_{DET(S)} + 1.0\text{ V}$ is applied to the SENSE pin to when V_{RO} reaches 50% of V_{IN} .

3. Overall

Table 10

($V_{IN} = 16.0\text{ V}$, $T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit
Current consumption during operation*1	I_{SS1}	$V_{SENSE} = +V_{DET(S)} + 1.0\text{ V}$, $I_{OUT} = 0\text{ mA}$	–	2.0	4.3	μA	7
Current consumption during detector detection*1	I_{SS2}	$V_{SENSE} = -V_{DET(S)} - 1.0\text{ V}$, $I_{OUT} = 0\text{ mA}$	–	0.5	1.4	μA	7

*1. The current flowing through the SENSE pin resistance is not included.

■ Test Circuits

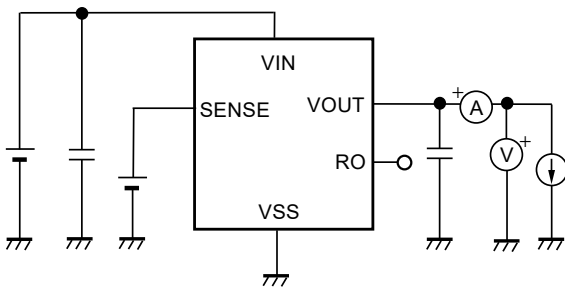


Figure 6 Test Circuit 1

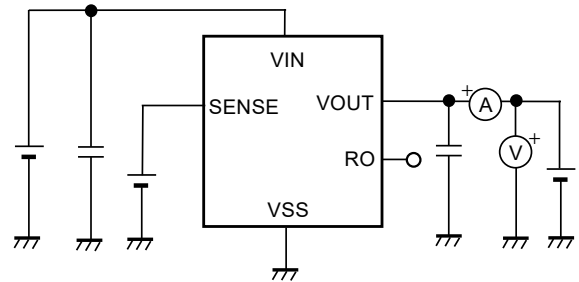


Figure 7 Test Circuit 2

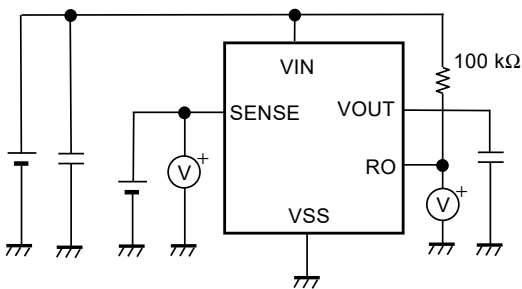


Figure 8 Test Circuit 3

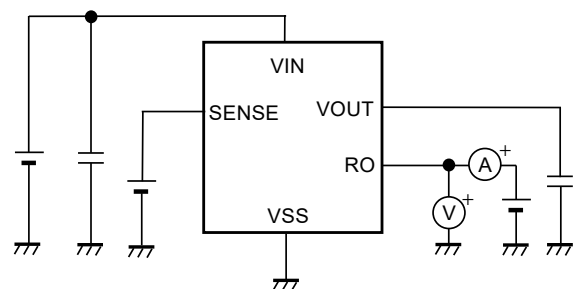


Figure 9 Test Circuit 4

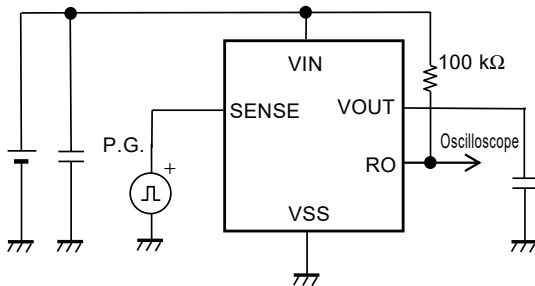


Figure 10 Test Circuit 5

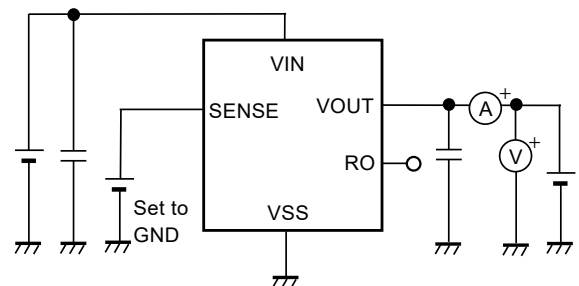


Figure 11 Test Circuit 6

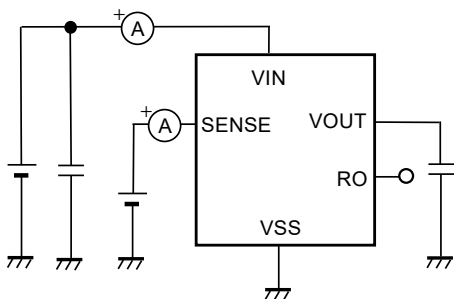
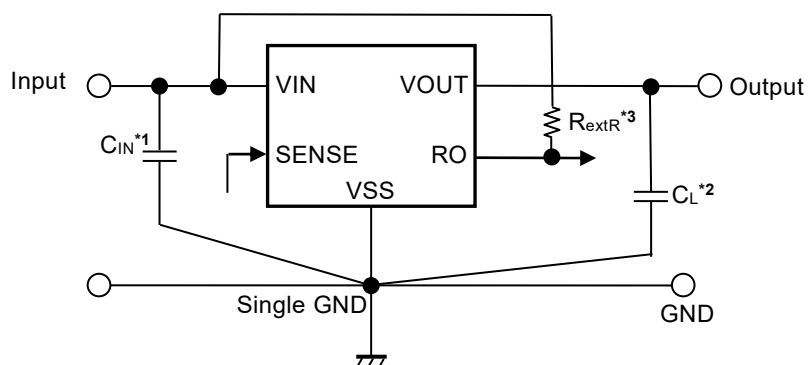


Figure 12 Test Circuit 7

■ Standard Circuit



- *1. C_{IN} is a capacitor for stabilizing the input.
- *2. C_L is a capacitor for stabilizing the output.
- *3. R_{extR} is the external pull-up resistor for the reset output pin.

Figure 13

Caution The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation including the temperature characteristics with an actual application to set the constants.

■ Condition of Application

Input capacitor (C_{IN}): A ceramic capacitor with capacitance of 1.0 μ F or more is recommended.
Output capacitor (C_L): A ceramic capacitor with capacitance of 1.0 μ F or more is recommended.

Caution Generally, in a voltage regulator, an oscillation may occur depending on the selection of the external parts. Perform thorough evaluation including the temperature characteristics with an actual application using the above capacitors to confirm no oscillation occurs.

■ Selection of Input Capacitor (C_{IN}) and Output Capacitor (C_L)

The S-19315 Series requires C_L between the VOUT pin and the VSS pin for phase compensation.

The operation is stabilized by a ceramic capacitor with capacitance of 1.0 μ F or more. When using an OS capacitor, a tantalum capacitor or an aluminum electrolytic capacitor, the capacitance also must be 1.0 μ F or more. However, an oscillation may occur depending on the equivalent series resistance (ESR).

Moreover, the S-19315 Series requires C_{IN} between the VIN pin and the VSS pin for a stable operation.

Generally, an oscillation may occur when a voltage regulator is used under the condition that the impedance of the power supply is high.

Note that the output voltage (V_{OUT}) transient characteristics varies depending on the capacitance of C_{IN} and C_L and the value of ESR.

Caution Perform thorough evaluation including the temperature characteristics with an actual application to select C_{IN} and C_L .

■ Explanation of Terms

1. Regulator block

1.1 Low dropout voltage regulator

This is a voltage regulator which made dropout voltage small by its built-in low on-resistance output transistor.

1.2 Output voltage (V_{OUT})

This voltage is output at an accuracy of $\pm 2.0\%$ or $\pm 0.03\text{ V}^2$ when the input voltage, the output current and the temperature are in a certain condition*1.

*1. Differs depending on the product.

*2. When $V_{OUT} < 1.5\text{ V}$: $\pm 0.03\text{ V}$, when $V_{OUT} \geq 1.5\text{ V}$: $\pm 2.0\%$

Caution If the certain condition is not satisfied, the output voltage may exceed the accuracy range of $\pm 2.0\%$ or $\pm 0.03\text{ V}$. Refer to "1. Regulator block" in "■ Electrical Characteristics" and "1. Regulator block" in "■ Characteristics (Typical Data)" for details.

1.3 Line regulation $\left(\frac{\Delta V_{OUT1}}{\Delta V_{IN} \bullet V_{OUT}} \right)$

Indicates the dependency of the output voltage against the input voltage. That is, the value shows how much the output voltage changes due to a change in the input voltage after fixing output current constant.

1.4 Load regulation (ΔV_{OUT2})

Indicates the dependency of the output voltage against the output current. That is, the value shows how much the output voltage changes due to a change in the output current after fixing input voltage constant.

1.5 Dropout voltage (V_{drop})

Indicates the difference between input voltage (V_{IN1}) and the output voltage when the output voltage becomes 98% of the output voltage value (V_{OUT3}) at $V_{IN} = 4.0\text{ V}$ ($1.0\text{ V} \leq V_{OUT(S)} < 2.0\text{ V}$) or $V_{IN} = V_{OUT(S)} + 2.0\text{ V}$ ($2.0\text{ V} \leq V_{OUT(S)} \leq 5.3\text{ V}$) after the input voltage (V_{IN}) is decreased gradually.

$$V_{drop} = V_{IN1} - (V_{OUT3} \times 0.98)$$

2. Detector block

2.1 Detection voltage ($-V_{DET}$)

The detection voltage is a voltage at which the output of the RO pin turns to "L".
 The detection voltage varies slightly among products of the same specification. The variation of detection voltage between the specified minimum ($-V_{DET\ min.}$) and the maximum ($-V_{DET\ max.}$) is called the detection voltage range (Refer to **Figure 14**).

2.2 Release voltage ($+V_{DET}$)

The release voltage is a voltage at which the output of the RO pin turns to "H".
 The release voltage varies slightly among products of the same specification. The variation of release voltage between the specified minimum ($+V_{DET\ min.}$) and the maximum ($+V_{DET\ max.}$) is called the release voltage range (Refer to **Figure 15**).

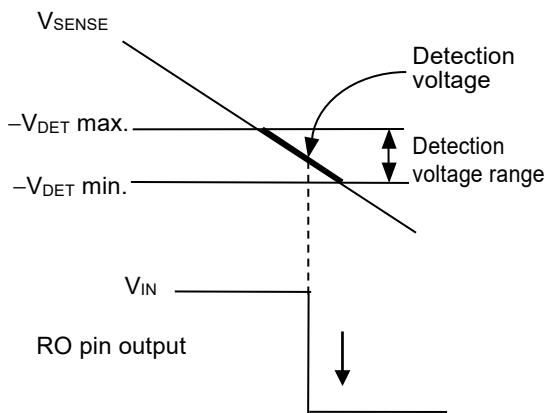


Figure 14 Detection Voltage

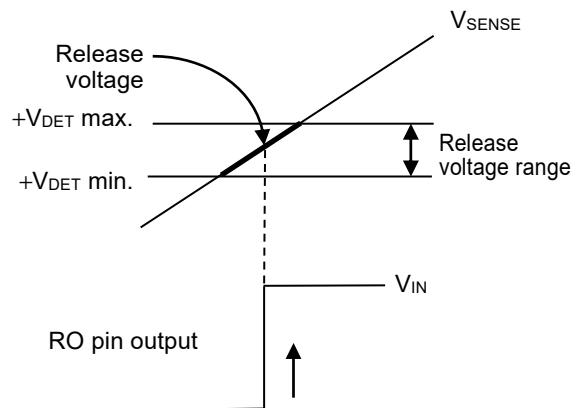


Figure 15 Release Voltage

2.3 Hysteresis width (V_{HYS})

The hysteresis width is the voltage difference between the detection voltage and the release voltage.
 Setting the hysteresis width between the detection voltage and the release voltage prevents malfunction caused by noise on the SENSE pin voltage (V_{SENSE}).

■ **Operation**

1. Regulator block

1.1 Basic operation

Figure 16 shows the block diagram of the regulator block to describe the basic operation.

The error amplifier compares the feedback voltage (V_{fb}) whose output voltage (V_{OUT}) is divided by the feedback resistors (R_s and R_f) with the reference voltage (V_{ref}). The error amplifier controls the output transistor, consequently, the regulator starts the operation that keeps V_{OUT} constant without the influence of the input voltage (V_{IN}).

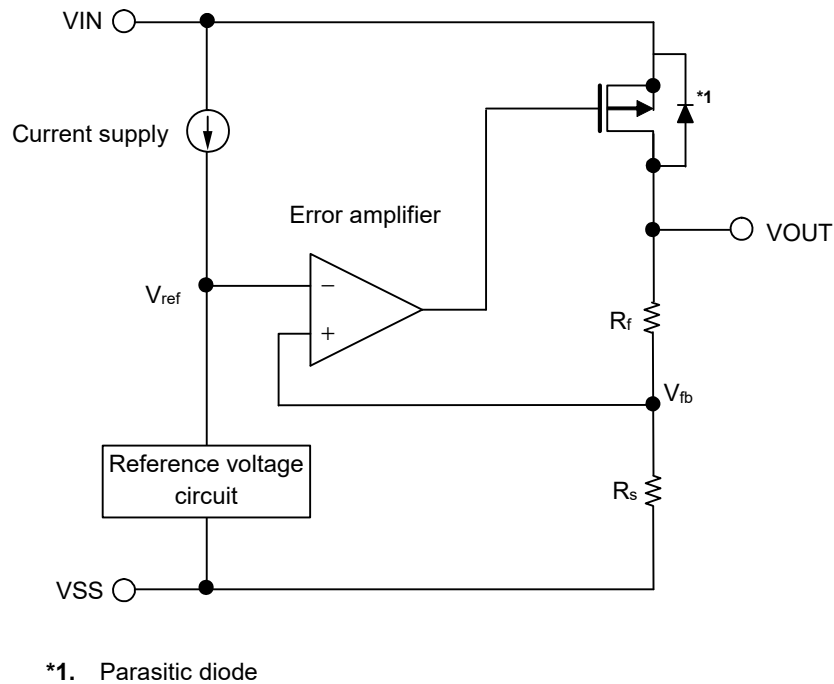


Figure 16

1.2 Output transistor

In the S-19315 Series, a low on-resistance P-channel MOS FET is used between the VIN pin and the VOUT pin as the output transistor. In order to keep V_{OUT} constant, the on-resistance of the output transistor varies appropriately according to the output current (I_{OUT}).

Caution Since a parasitic diode exists between the VIN pin and the VOUT pin due to the structure of the transistor, the IC may be damaged by a reverse current if V_{OUT} becomes higher than V_{IN} . Therefore, be sure that V_{OUT} does not exceed $V_{IN} + 0.3$ V.

1.3 ON / OFF circuit

The ON / OFF circuit controls the internal circuit and the output transistor in order to start and stop the regulator. When the detector becomes the detection status, the internal circuit of regulator stops operating and the output transistor between the VIN pin and the VOUT pin is turned off, reducing current consumption significantly.

Table 11

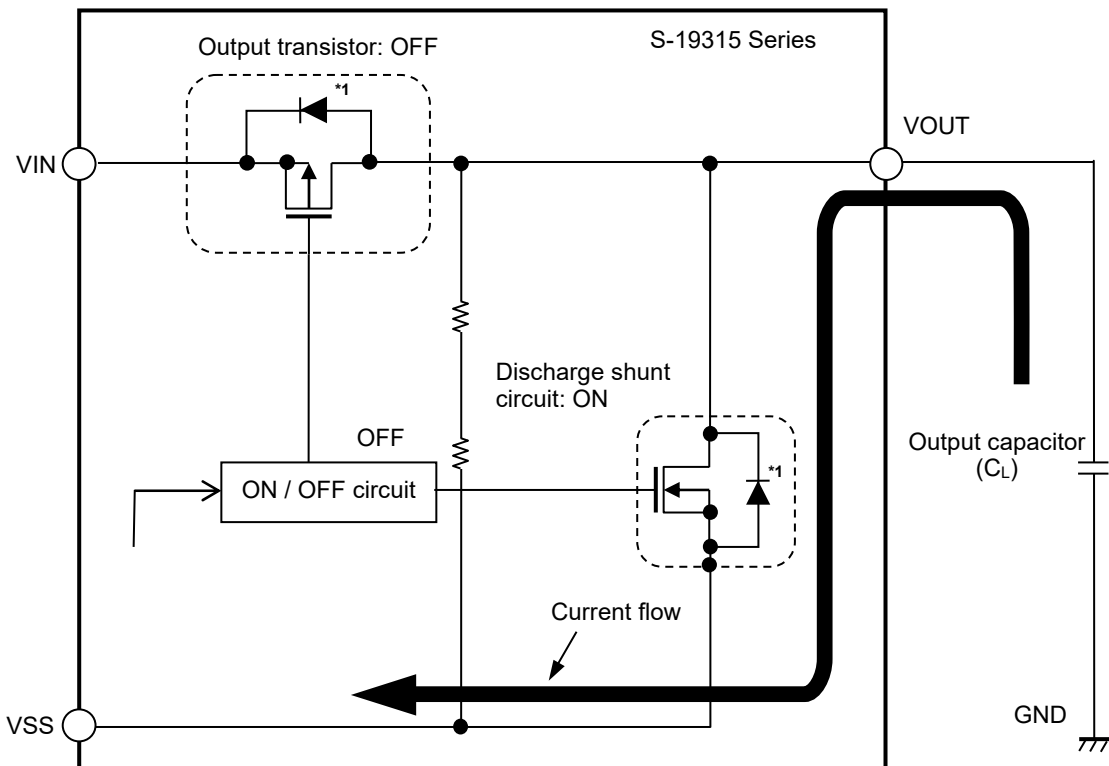
Detector	ON / OFF Circuit	Regulator Internal Circuit	VOUT Pin Voltage	Current Consumption
Released	ON	Operate	Constant value*1	I _{SS1}
Detected	OFF	Stop	Pulled down to V _{SS} *2	I _{SS2}

- *1. The constant value is output due to the regulating based on the set output voltage value.
- *2. The VOUT pin voltage is pulled down to V_{SS} due to combined resistance (R_{Low} = 650 Ω typ.) of the discharge shunt circuit and the feedback resistors, and a load.

1.4 Discharge shunt function

The S-19315 Series has a built-in discharge shunt circuit to discharge the output capacitance. The output capacitance is discharged as follows so that the VOUT pin reaches the V_{SS} level.

- (1) The ON / OFF circuit is turned OFF.
- (2) The output transistor is turned off.
- (3) The discharge shunt circuit is turned on.
- (4) The output capacitor discharges.



*1. Parasitic diode

Figure 17

1.5 Overcurrent protection circuit

The S-19315 Series has a built-in overcurrent protection circuit to limit the overcurrent of the output transistor. When the V_{OUT} pin is shorted to the V_{SS} pin, that is, at the time of the output short-circuit, the output current is limited to 24 mA typ. due to the overcurrent protection circuit operation. The S-19315 Series restarts regulating when the output transistor is released from the overcurrent status.

Caution This overcurrent protection circuit does not work as for thermal protection. For example, when the output transistor keeps the overcurrent status long at the time of output short-circuit or due to other reasons, pay attention to the conditions of the input voltage and the load current so as not to exceed the power dissipation.

1.6 Thermal shutdown circuit

The S-19315 Series has a built-in thermal shutdown circuit to limit overheating. When the junction temperature increases to 160°C typ., the thermal shutdown circuit becomes the detection status, and the regulating is stopped. When the junction temperature decreases to 135°C typ., the thermal shutdown circuit becomes the release status, and the regulator is restarted.

If the thermal shutdown circuit becomes the detection status due to self-heating, the regulating is stopped and V_{OUT} decreases. For this reason, the self-heating is limited and the temperature of the IC decreases. The thermal shutdown circuit becomes release status when the temperature of the IC decreases, and the regulating is restarted thus the self-heating is generated again. Repeating this procedure makes the waveform of V_{OUT} into a pulse-like form. This phenomenon continues unless decreasing either or both of the input voltage and the output current in order to reduce the internal power consumption, or decreasing the ambient temperature. Note that the product may suffer physical damage such as deterioration if the above phenomenon occurs continuously.

Caution If a large load current flows during the restart process of regulating after the thermal shutdown circuit changes to the release status from the detection status, the thermal shutdown circuit becomes the detection status again due to self-heating, and a problem may happen in the restart of regulating. A large load current, for example, occurs when charging to the C_L whose capacitance is large. Perform thorough evaluation including the temperature characteristics with an actual application to select C_L.

Table 12

Thermal Shutdown Circuit	V _{OUT} Pin Voltage
Release: 135°C typ.*1	Constant value*2
Detection: 160°C typ.*1	Pulled down to V _{SS} *3

*1. Junction temperature

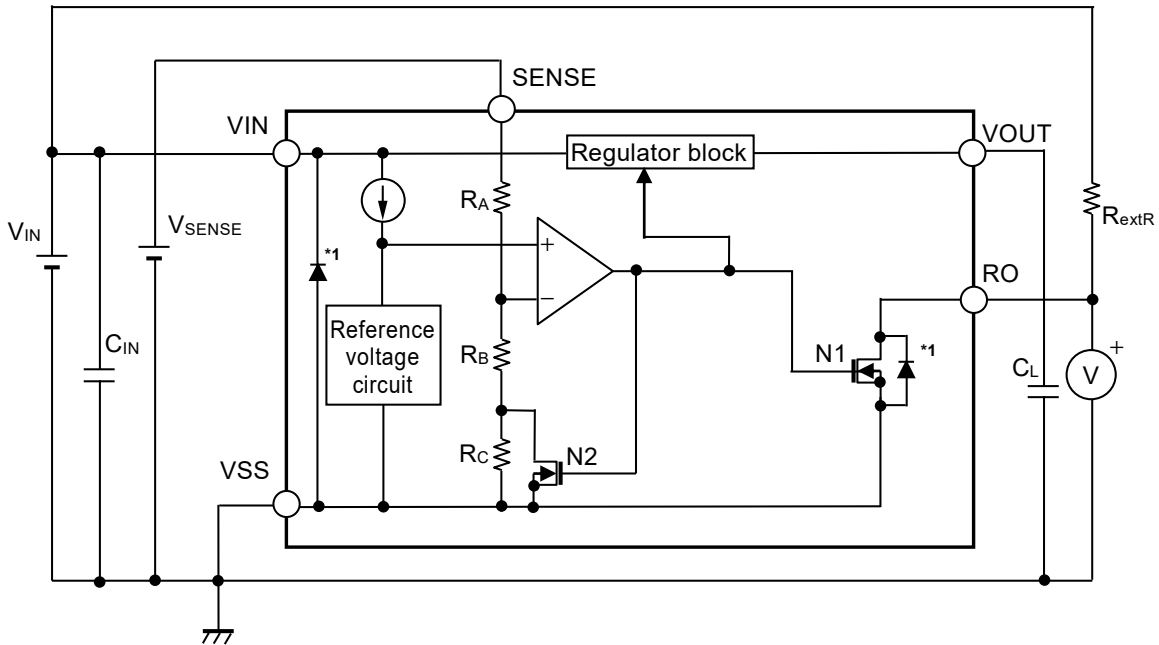
*2. The constant value is output due to the regulating based on the set output voltage value.

*3. The V_{OUT} pin voltage is pulled down to V_{SS} due to the feedback resistors (R_s and R_f) and a load.

2. Detector block

2.1 Basic operation

- (1) When the input voltage (V_{IN}) is the minimum operation voltage or higher, and the SENSE pin voltage (V_{SENSE}) is the release voltage ($+V_{DET}$) or higher, the Nch transistor (N1) is off, and the RO pin output is "H".
 Since the Nch transistor (N2) is off, the input voltage to the comparator is $\frac{(R_B + R_C) \cdot V_{SENSE}}{R_A + R_B + R_C}$.
- (2) Even if V_{SENSE} decreases to $+V_{DET}$ or lower, the RO pin output is "H" when V_{SENSE} is the detection voltage ($-V_{DET}$) or higher. When V_{SENSE} is $-V_{DET}$ (point A in **Figure 19**) or lower, N1 is on, and the RO pin output is "L".
 At this time, N2 is turned on, and the input voltage to the comparator is $\frac{R_B \cdot V_{SENSE}}{R_A + R_B}$.
- (3) Even if V_{SENSE} further decreases to the IC's minimum operation voltage or lower, the RO pin output is stable when V_{IN} is the minimum operation voltage or higher.
- (4) Even if V_{SENSE} exceeds $-V_{DET}$, the RO pin output is "L" when V_{SENSE} is lower than $+V_{DET}$.
- (5) When V_{SENSE} further increases to $+V_{DET}$ (point B in **Figure 19**) or higher, the RO pin output is "H".



*1. Parasitic diode

Figure 18 Operation

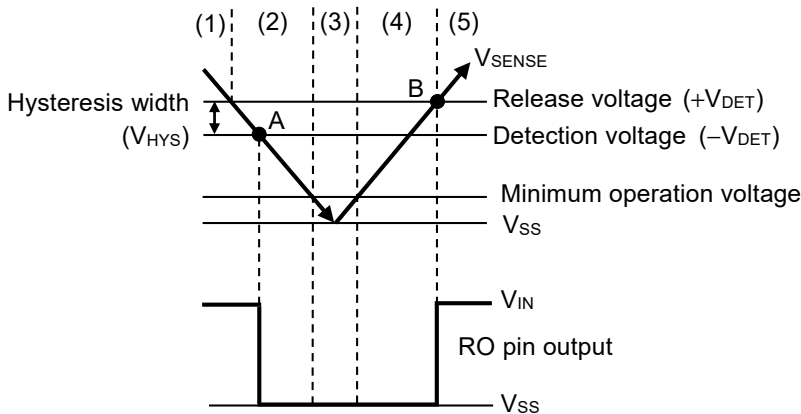


Figure 19 Timing Chart

2.2 SENSE pin

2.2.1 Error when detection voltage is set externally

By connecting a node that was resistance-divided by the resistor (R_A) and the resistor (R_B) to the SENSE pin as seen in **Figure 20**, the detection voltage can be set externally. Although the internal resistance (R_{SENSE}) in the S-19315 Series is large (13 MΩ min.) to make the error in the current flowing through R_{SENSE} small, R_A and R_B should be selected such that the error is within the allowable limits.

If the V_{SENSE} greatly exceeds the $+V_{DET}$, the current flowing through R_{SENSE} is limited.

2.2.2 Selection of R_A and R_B

In **Figure 20**, the relation between the external setting detection voltage (V_{DX}) and the actual detection voltage ($-V_{DET}$) is ideally calculated by the equation below.

$$V_{DX} = -V_{DET} \times \left(1 + \frac{R_A}{R_B}\right) \quad \dots (1)$$

However, in reality there is an error in the current flowing through R_{SENSE} .

When considering this error, the relation between V_{DX} and $-V_{DET}$ is calculated as follows.

$$\begin{aligned} V_{DX} &= -V_{DET} \times \left(1 + \frac{R_A}{R_B \parallel R_{SENSE}}\right) \\ &= -V_{DET} \times \left(1 + \frac{R_A}{\frac{R_B \times R_{SENSE}}{R_B + R_{SENSE}}}\right) \\ &= -V_{DET} \times \left(1 + \frac{R_A}{R_B}\right) + \frac{R_A}{R_{SENSE}} \times -V_{DET} \quad \dots (2) \end{aligned}$$

By using equations (1) and (2), the error is calculated as $-V_{DET} \times \frac{R_A}{R_{SENSE}}$.

The error rate is calculated as follows by dividing the error by the right-hand side of equation (1).

$$\frac{R_A \times R_B}{R_{SENSE} \times (R_A + R_B)} \times 100 [\%] = \frac{R_A \parallel R_B}{R_{SENSE}} \times 100 [\%] \quad \dots (3)$$

As seen in equation (3), the smaller the resistance values of R_A and R_B compared to R_{SENSE} , the smaller the error rate becomes.

Also, the relation between the external setting hysteresis width (V_{HX}) and the hysteresis width (V_{HYS}) is calculated by equation below. Error due to R_{SENSE} also occurs to the relation in a similar way to the detection voltage.

$$V_{HX} = V_{HYS} \times \left(1 + \frac{R_A}{R_B}\right) \quad \dots (4)$$

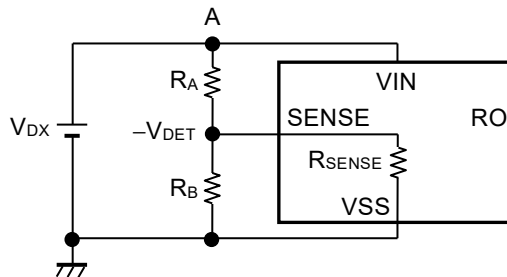


Figure 20 Detection Voltage External Setting Circuit

- Caution 1.** If R_A and R_B are large, the SENSE pin input impedance becomes higher and may cause a malfunction due to noise. In this case, connect a capacitor between the SENSE pin and the VSS pin.
- 2.** If the parasitic resistance and parasitic inductance between V_{DX} and point A and between point A and VIN pin are respectively larger, oscillation may occur. Perform thorough evaluation using the actual application.

2.3 Power on sequence

Apply power in the order, the VIN pin then the SENSE pin.

As seen in **Figure 21**, when $V_{SENSE} \geq +V_{DET}$, the RO pin output becomes "H", and the detector becomes the release status (normal operation).

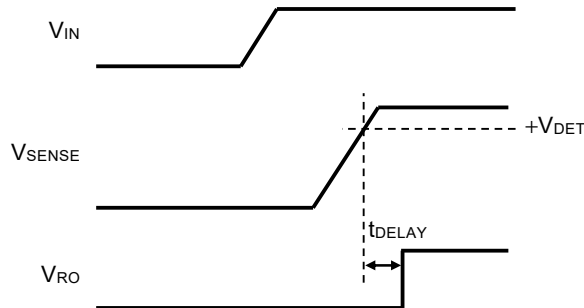


Figure 21

Caution If power is applied in the order the SENSE pin then the VIN pin, an erroneous release may occur even if $V_{SENSE} < +V_{DET}$.

2.4 SENSE pin voltage glitch (reference)

2.4.1 Detection operation

Figure 22 shows the relation between pulse width and pulse voltage difference (V_{OD}) where the release status can be maintained when a pulse equal to or lower than the detection voltage ($-V_{DET}$) is input to the SENSE pin during the release status.

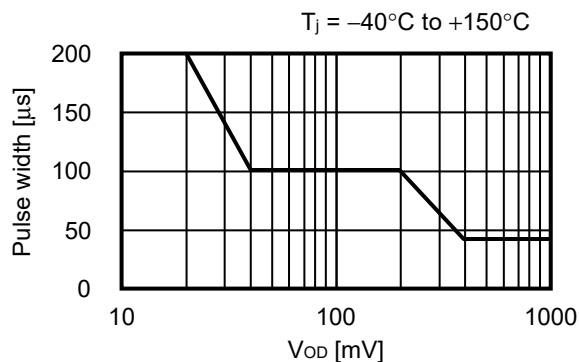
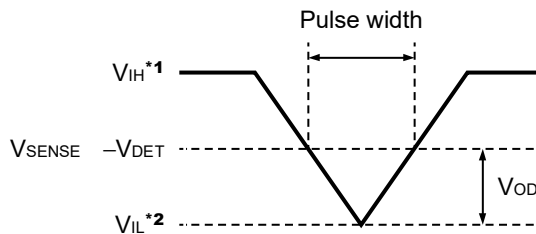


Figure 22



*1. $V_{IH} = 16.0$ V

*2. $V_{IL} = -V_{DET} - V_{OD}$

Figure 23 SENSE Pin Input Voltage Waveform

Caution **Figure 22** shows the pulse conditions which can maintain the release status. If the pulse whose pulse width and V_{OD} are larger than these conditions is input to the SENSE pin, the RO pin may change to a detection status.

2. 4. 2 Release operation

Figure 24 shows the relation between pulse width and pulse voltage difference (V_{OD}) where the detection status can be maintained when a pulse equal to or higher than the release voltage ($+V_{DET}$) is input to the SENSE pin during detection status.

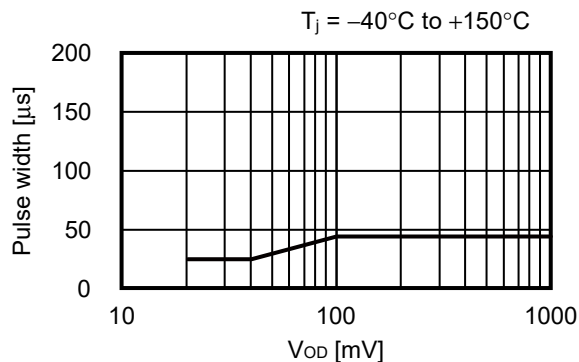
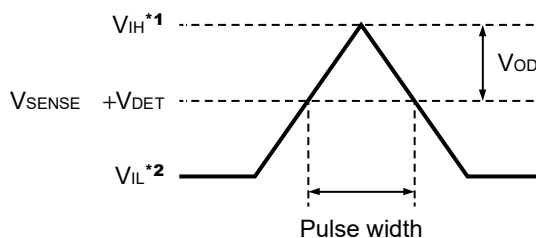


Figure 24



- *1. $V_{IH} = +V_{DET} + V_{OD}$
- *2. $V_{IL} = +V_{DET} - 1.0 \text{ V}$

Figure 25 SENSE Pin Input Voltage Waveform

Caution Figure 24 shows the pulse conditions which can maintain the detection status. If the pulse whose a pulse width and V_{OD} are larger than these conditions is input to the SENSE pin, the RO pin may change to a release status.

■ Precautions

- Generally, when a voltage regulator is used under the condition that the impedance of the power supply is high, an oscillation may occur. Perform thorough evaluation including the temperature characteristics with an actual application to select C_{IN} .
- Generally, in a voltage regulator, an oscillation may occur depending on the selection of the external parts. The following use conditions are recommended in the S-19315 Series; however, perform thorough evaluation including the temperature characteristics with an actual application to select C_{IN} and C_L .

Input capacitor (C_{IN}): A ceramic capacitor with capacitance of 1.0 μ F or more is recommended.

Output capacitor (C_L): A ceramic capacitor with capacitance of 1.0 μ F or more is recommended.

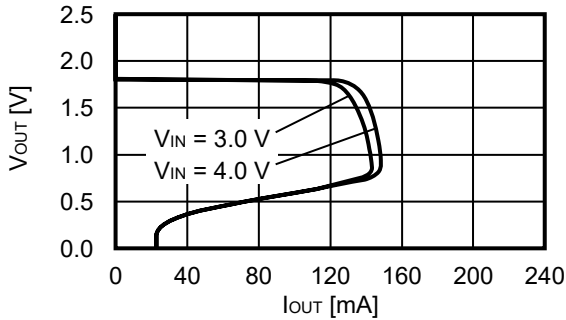
- Generally, in a voltage regulator, the values of an overshoot and an undershoot in the output voltage vary depending on the variation factors of input voltage start-up, input voltage fluctuation, load fluctuation etc., or the capacitance of C_{IN} or C_L and the value of the equivalent series resistance (ESR), which may cause a problem to the stable operation. Perform thorough evaluation including the temperature characteristics with an actual application to select C_{IN} and C_L .
- Generally, in a voltage regulator, an overshoot may occur in the output voltage momentarily if the input voltage steeply changes when the input voltage is started up, the input voltage fluctuates, etc. Perform thorough evaluation including the temperature characteristics with an actual application to confirm no problems happen.
- Generally, in a voltage regulator, if the VOUT pin is steeply shorted with GND, a negative voltage exceeding the absolute maximum ratings may occur in the VOUT pin due to resonance phenomenon of the inductance and the capacitance including C_L on the application. The resonance phenomenon is expected to be weakened by inserting a series resistor into the resonance path, and the negative voltage is expected to be limited by inserting a protection diode between the VOUT pin and the VSS pin.
- If the input voltage is started up steeply under the condition that the capacitance of C_L is large, the thermal shutdown circuit may be in the detection status by self-heating due to the charge current to C_L .
- Make sure of the conditions for the input voltage, output voltage and the load current so that the internal loss does not exceed the power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- When considering the output current value that the IC is able to output, make sure of the output current value specified in **Table 8** in "■ Electrical Characteristics" and footnote *4 of the table.
- Wiring patterns on the application related to the VIN pin, the VOUT pin and the VSS pin should be designed so that the impedance is low. When mounting C_{IN} between the VIN pin and the VSS pin and C_L between the VOUT pin and the VSS pin, connect the capacitors as close as possible to the respective destination pins of the IC.
- Because the SENSE pin has a high impedance, malfunctions may occur due to noise. Be careful of wiring adjoining SENSE pin wiring in actual applications.
- In the package equipped with heat sink of backside, mount the heat sink firmly. Since the heat radiation differs according to the condition of the application, perform thorough evaluation with an actual application to confirm no problems happen.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

■ **Characteristics (Typical Data)**

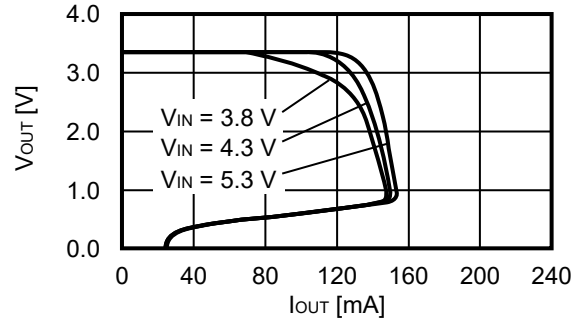
1. Regulator block

1.1 Output voltage vs. Output current (When load current increases) (Ta = +25°C)

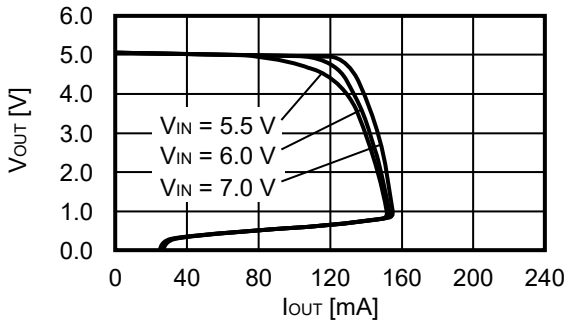
1.1.1 V_{OUT} = 1.8 V



1.1.2 V_{OUT} = 3.3 V



1.1.3 V_{OUT} = 5.0 V

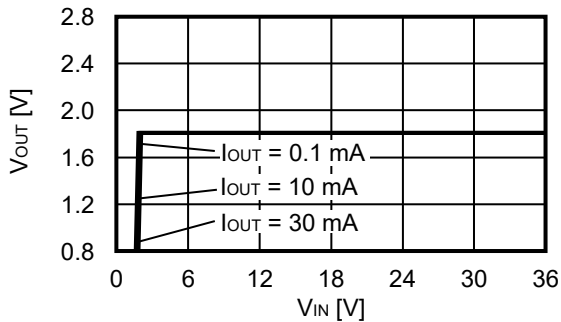


Remark In determining the output current, attention should be paid to the following.

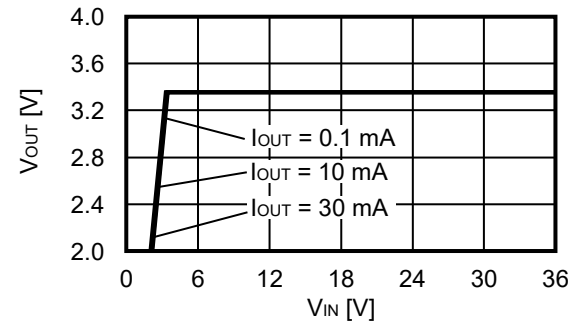
1. The minimum output current value and footnote *4 of **Table 8** in "■ **Electrical Characteristics**"
2. Power dissipation

1.2 Output voltage vs. Input voltage (Ta = +25°C)

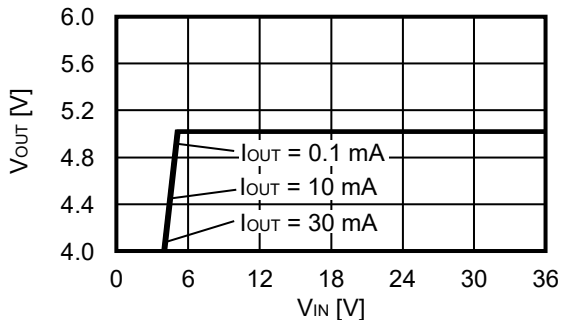
1.2.1 V_{OUT} = 1.8 V



1.2.2 V_{OUT} = 3.3 V

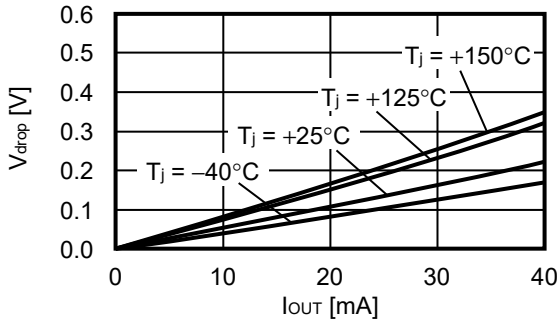


1.2.3 V_{OUT} = 5.0 V

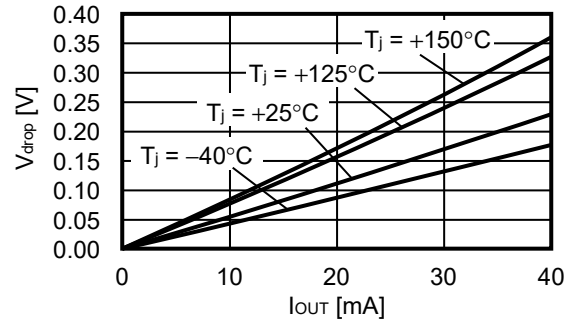


1.3 Dropout voltage vs. Output current

1.3.1 $V_{OUT} = 3.3\text{ V}$

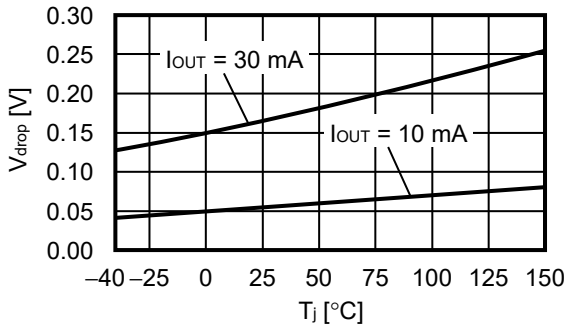


1.3.2 $V_{OUT} = 5.0\text{ V}$

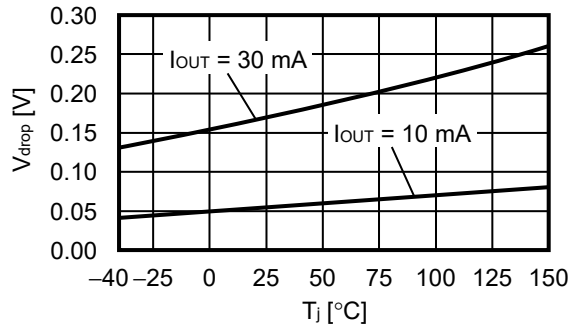


1.4 Dropout voltage vs. Junction temperature

1.4.1 $V_{OUT} = 3.3\text{ V}$

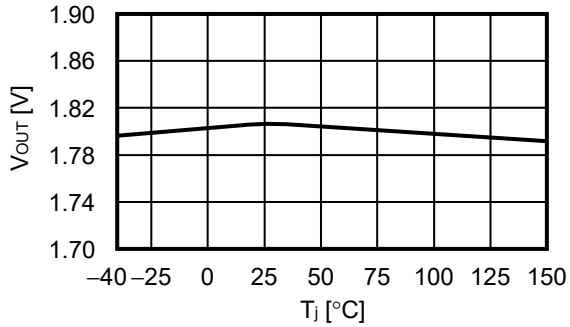


1.4.2 $V_{OUT} = 5.0\text{ V}$

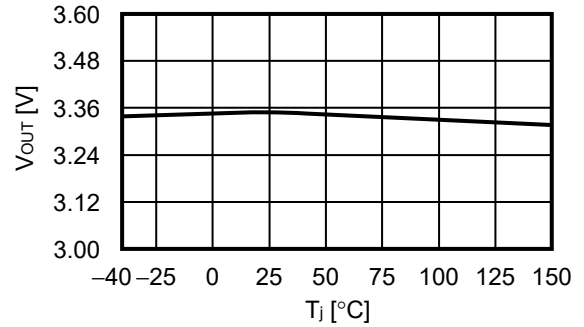


1.5 Output voltage vs. Junction temperature

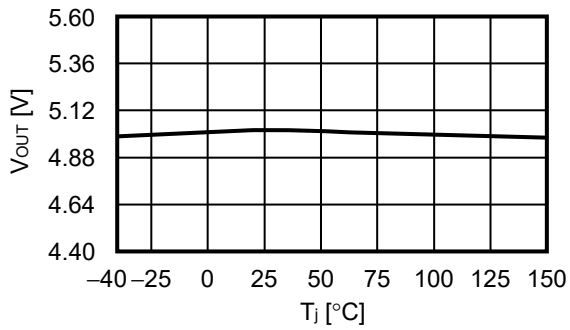
1.5.1 $V_{OUT} = 1.8\text{ V}$



1.5.2 $V_{OUT} = 3.3\text{ V}$

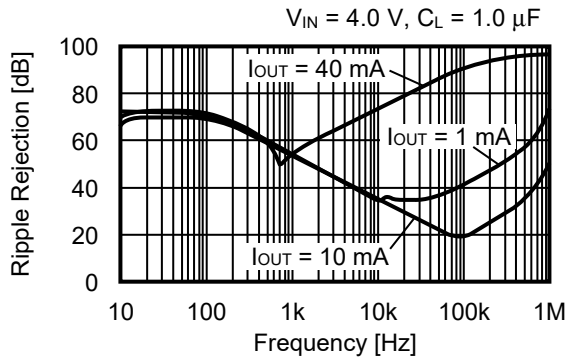


1.5.3 $V_{OUT} = 5.0\text{ V}$

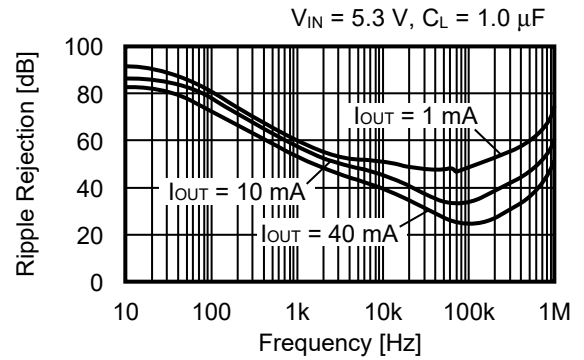


1.6 Ripple rejection ($T_a = +25^\circ\text{C}$)

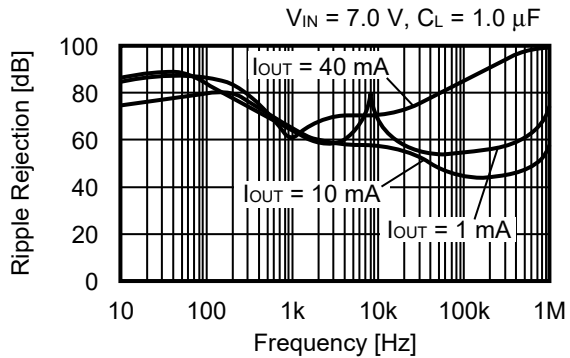
1.6.1 $V_{OUT} = 1.8\text{ V}$



1.6.2 $V_{OUT} = 3.3\text{ V}$



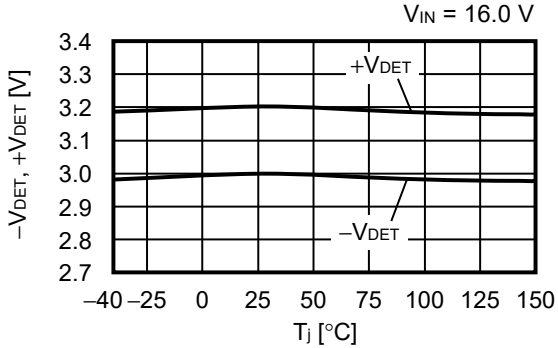
1.6.3 $V_{OUT} = 5.0\text{ V}$



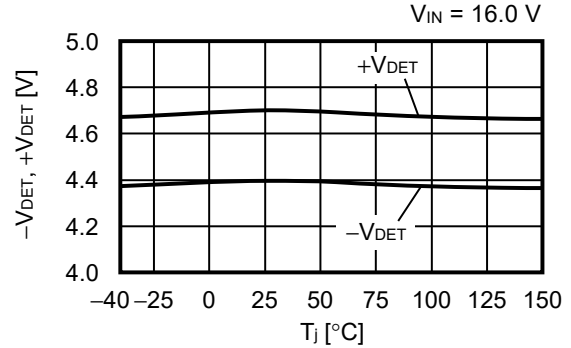
2. Detector block

2.1 Detection voltage, Release voltage vs. Junction temperature

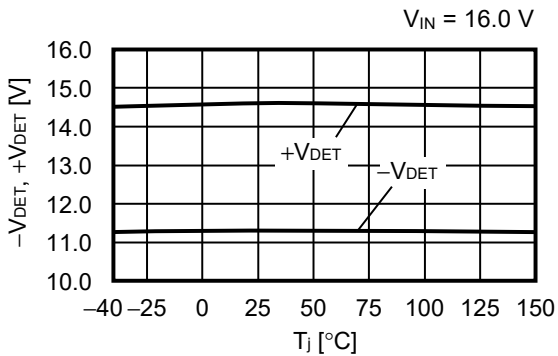
2.1.1 $-V_{DET} = 3.0\text{ V}$, $+V_{DET} = 3.2\text{ V}$



2.1.2 $-V_{DET} = 4.4\text{ V}$, $+V_{DET} = 4.7\text{ V}$

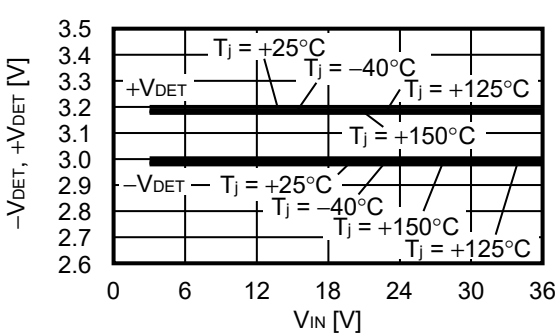


2.1.3 $-V_{DET} = 11.3\text{ V}$, $+V_{DET} = 14.6\text{ V}$

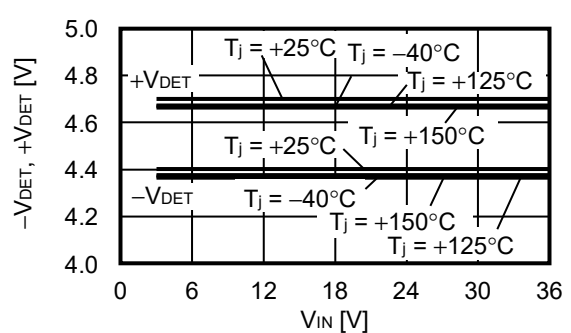


2.2 Detection voltage, Release voltage vs. Input voltage

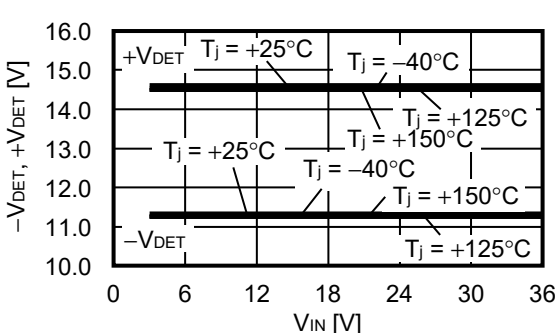
2.2.1 $-V_{DET} = 3.0\text{ V}$, $+V_{DET} = 3.2\text{ V}$



2.2.2 $-V_{DET} = 4.4\text{ V}$, $+V_{DET} = 4.7\text{ V}$

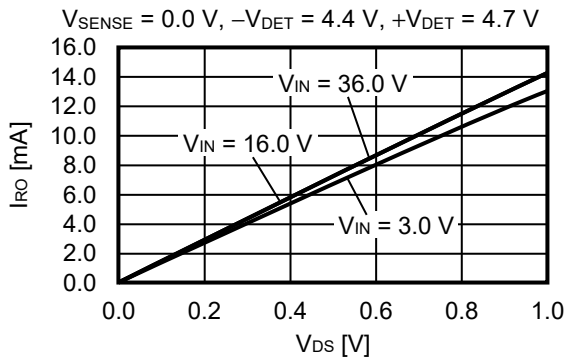


2.2.3 $-V_{DET} = 11.3\text{ V}$, $+V_{DET} = 14.6\text{ V}$

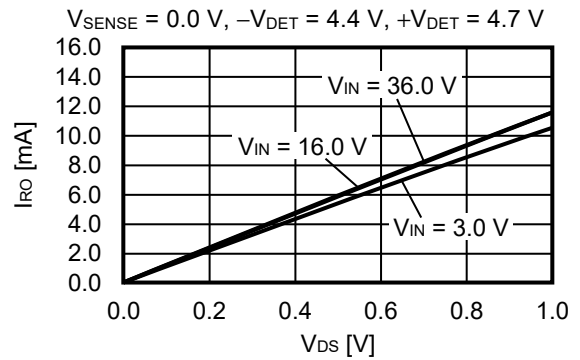


2.3 Nch transistor output current vs. V_{DS}

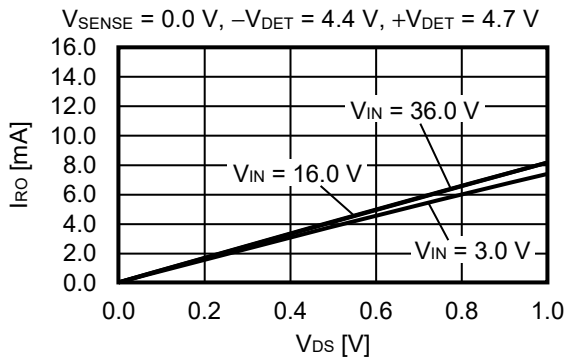
2.3.1 $T_a = -40^\circ\text{C}$



2.3.2 $T_a = +25^\circ\text{C}$

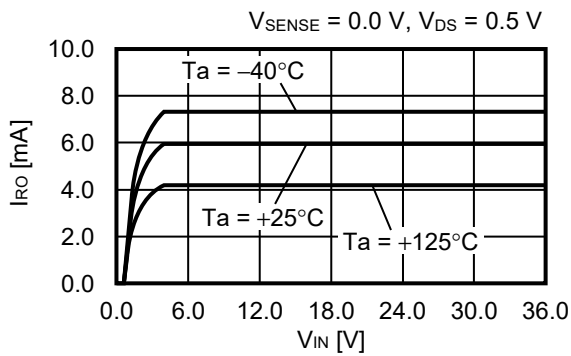


2.3.3 $T_a = +125^\circ\text{C}$



2.4 Nch transistor output current vs. Input voltage

2.4.1 $-V_{DET} = 11.3\text{ V}, +V_{DET} = 14.6\text{ V}$

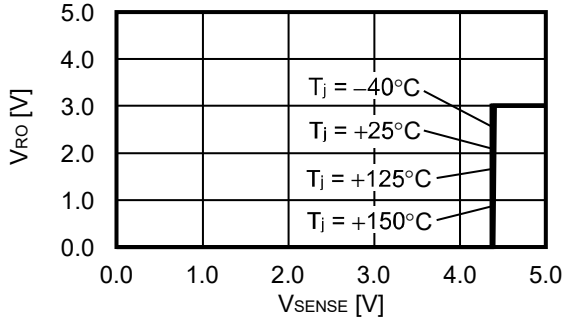


Remark V_{DS} : Drain-to-source voltage of the output transistor

2.5 Minimum operation voltage vs. SENSE pin voltage

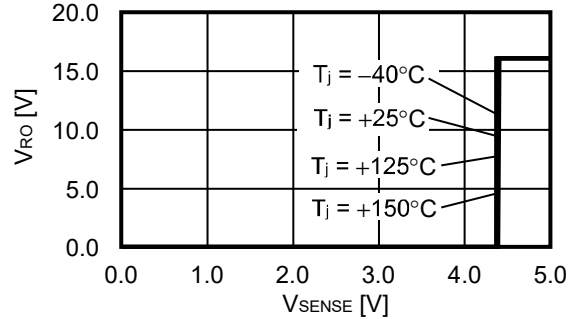
2.5.1 Pull-up to V_{IN}

$-V_{DET} = 4.4\text{ V}, +V_{DET} = 4.7\text{ V}$,
 Pull-up resistance: 100 k Ω , $V_{IN} = 3.0\text{ V}$



2.5.2 Pull-up to 16.0 V

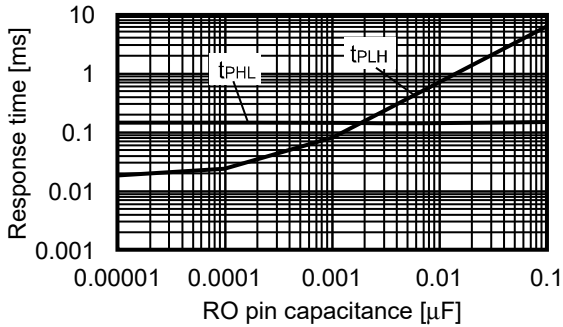
$-V_{DET} = 4.4\text{ V}, +V_{DET} = 4.7\text{ V}$,
 Pull-up resistance: 100 k Ω , $V_{IN} = 3.0\text{ V}$



2.6 Dynamic response vs. RO pin capacitance

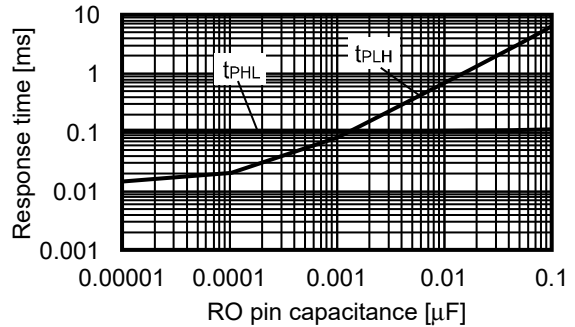
2.6.1 $T_a = -40^\circ\text{C}$

$-V_{DET} = 4.4\text{ V}, +V_{DET} = 4.7\text{ V}$



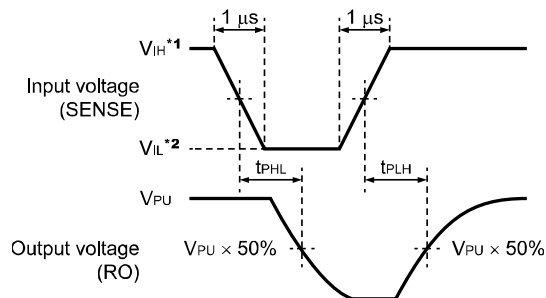
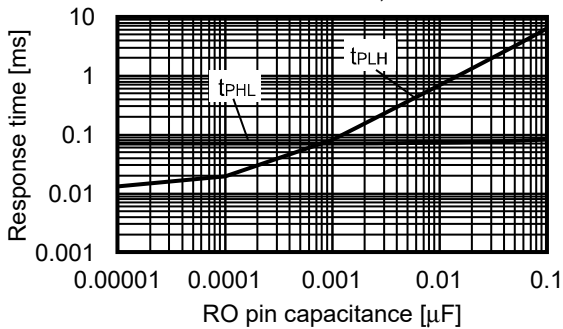
2.6.2 $T_a = +25^\circ\text{C}$

$-V_{DET} = 4.4\text{ V}, +V_{DET} = 4.7\text{ V}$



2.6.3 $T_a = +125^\circ\text{C}$

$-V_{DET} = 4.4\text{ V}, +V_{DET} = 4.7\text{ V}$



- *1. $V_{IH} = 36.0\text{ V}$
- *2. $V_{IL} = 0.0\text{ V}$

Figure 26 Test Condition of Response Time

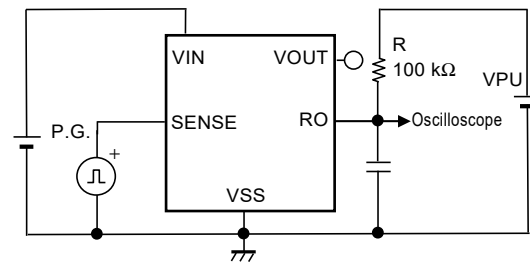


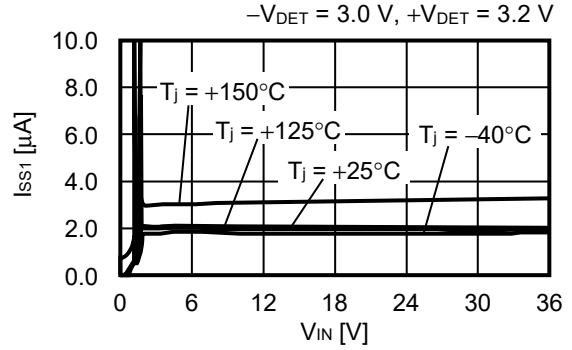
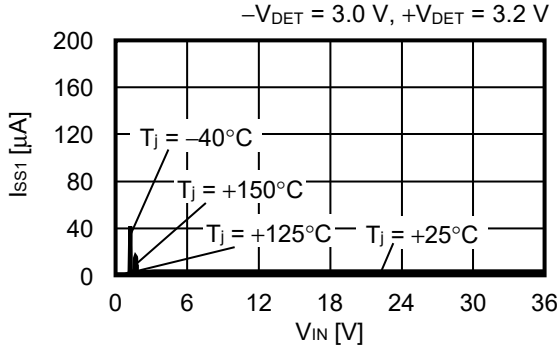
Figure 27 Test Circuit of Response Time

Caution The above connection diagram and constants will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constants.

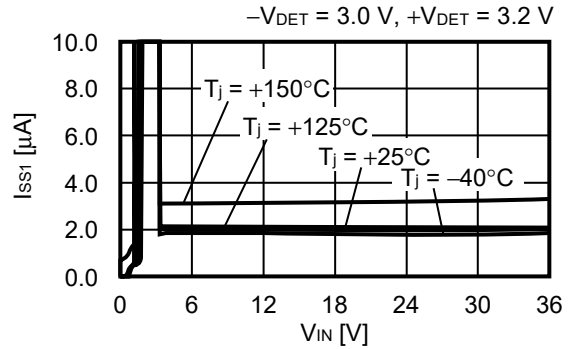
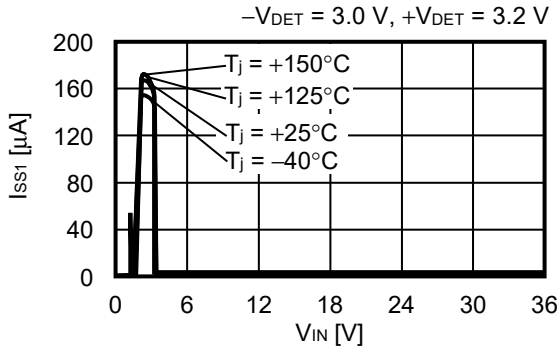
3. Overall

3.1 Current consumption during operation vs. Input voltage (When ON / OFF circuit is ON, no load)

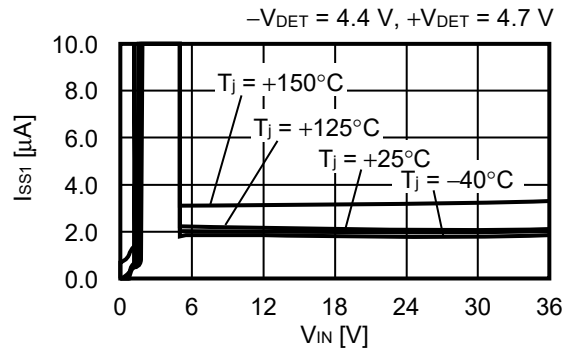
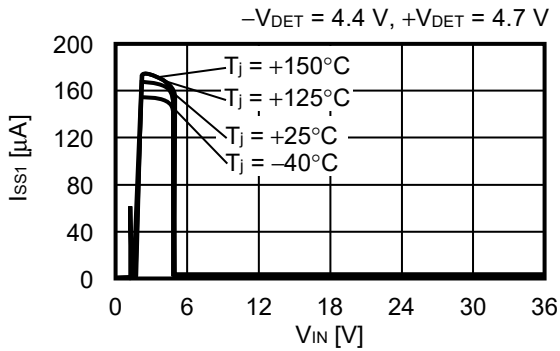
3.1.1 $V_{OUT} = 1.8\text{ V}$



3.1.2 $V_{OUT} = 3.3\text{ V}$

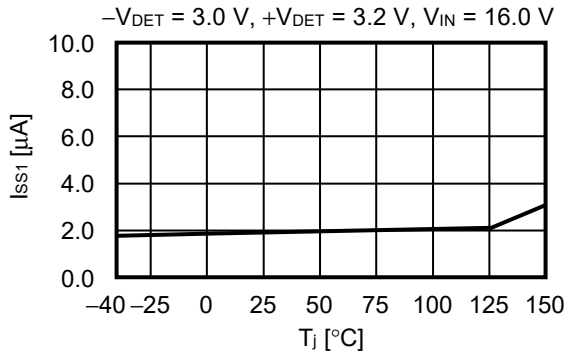


3.1.3 $V_{OUT} = 5.0\text{ V}$

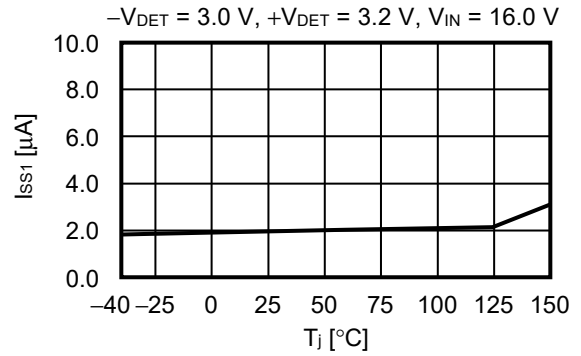


3.2 Current consumption during operation vs. Junction temperature

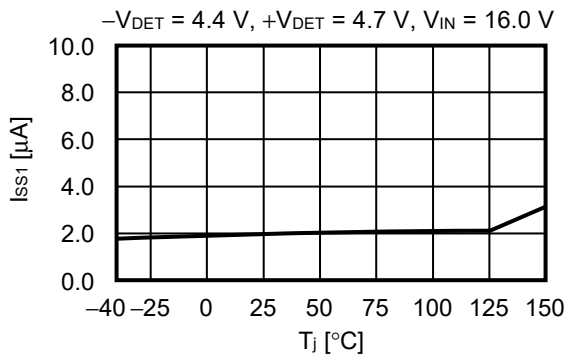
3.2.1 V_{OUT} = 1.8 V



3.2.2 V_{OUT} = 3.3 V

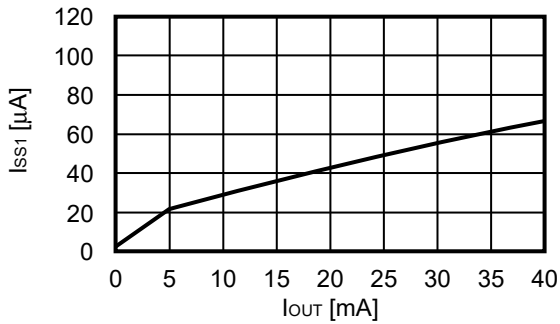


3.2.3 V_{OUT} = 5.0 V

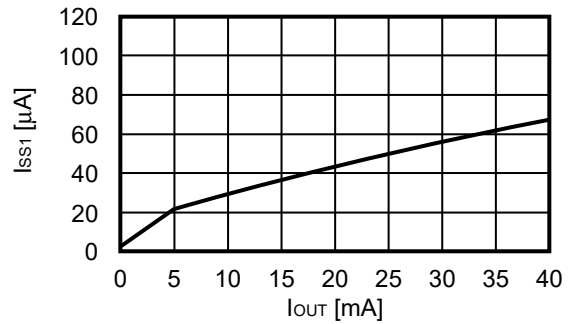


3.3 Current consumption during operation vs. Output current (T_a = +25°C)

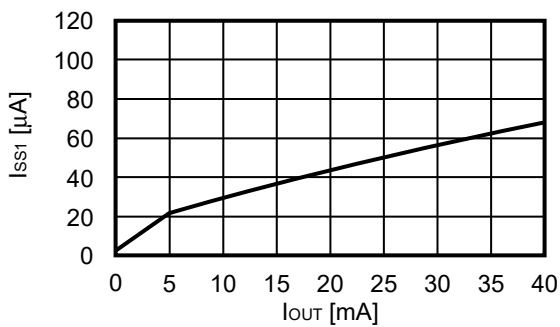
3.3.1 V_{OUT} = 1.8 V



3.3.2 V_{OUT} = 3.3 V



3.3.3 V_{OUT} = 5.0 V

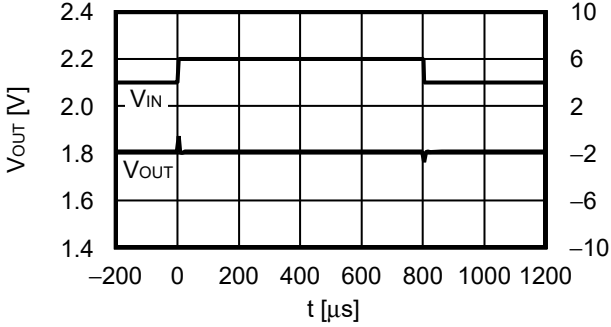


■ **Reference Data**

1. Transient response characteristics when input (Ta = +25°C)

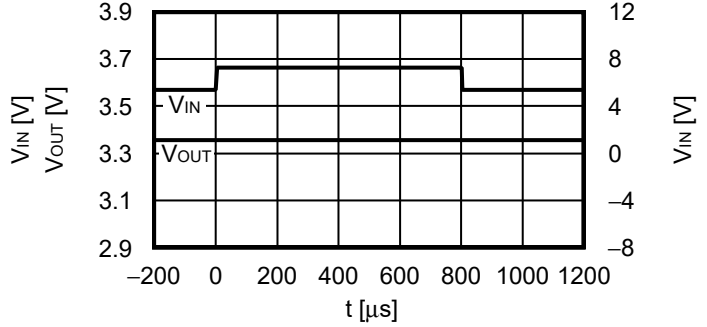
1.1 V_{OUT} = 1.8 V

I_{OUT} = 20 mA, C_L = 1.0 μF, V_{IN} = 4.0 V ↔ 6.0 V, t_r = t_f = 5.0 μs



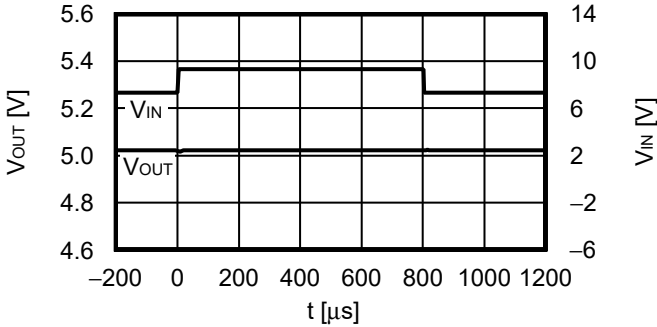
1.2 V_{OUT} = 3.3 V

I_{OUT} = 20 mA, C_L = 1.0 μF, V_{IN} = 5.3 V ↔ 7.3 V, t_r = t_f = 5.0 μs



1.3 V_{OUT} = 5.0 V

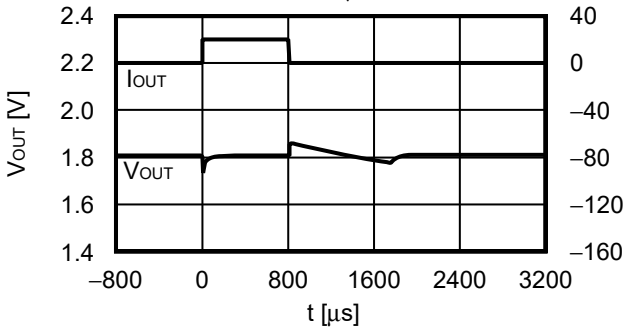
I_{OUT} = 20 mA, C_L = 1.0 μF, V_{IN} = 7.0 V ↔ 9.0 V, t_r = t_f = 5.0 μs



2. Transient response characteristics of load (Ta = +25°C)

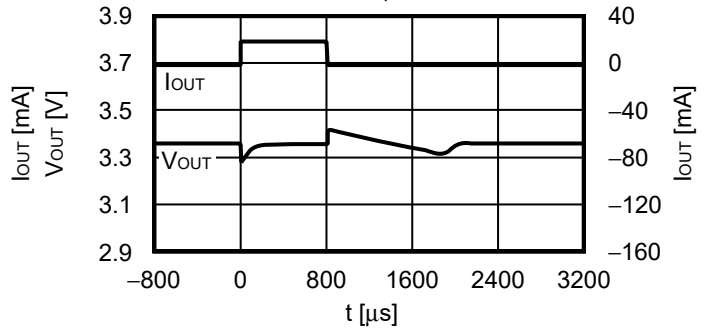
2.1 V_{OUT} = 1.8 V

V_{IN} = 4.0 V, C_{IN} = C_L = 1.0 μF, I_{OUT} = 0.1 mA ↔ 20 mA



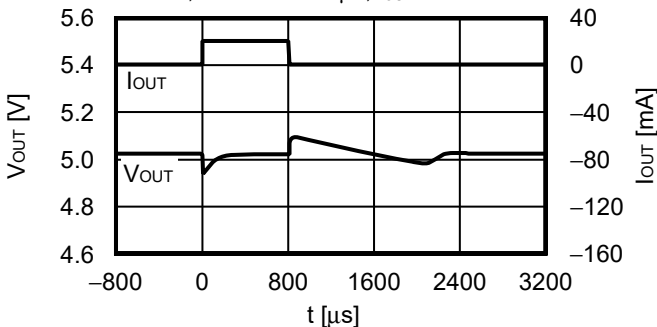
2.2 V_{OUT} = 3.3 V

V_{IN} = 5.3 V, C_{IN} = C_L = 1.0 μF, I_{OUT} = 0.1 mA ↔ 20 mA



2.3 V_{OUT} = 5.0 V

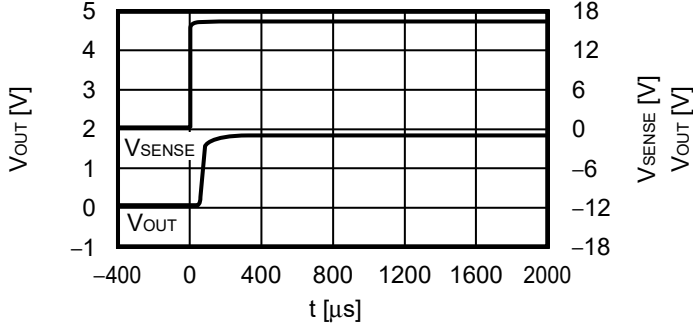
V_{IN} = 7.0 V, C_{IN} = C_L = 1.0 μF, I_{OUT} = 0.1 mA ↔ 20 mA



3. Transient response characteristics of SENSE pin (Ta = +25°C)

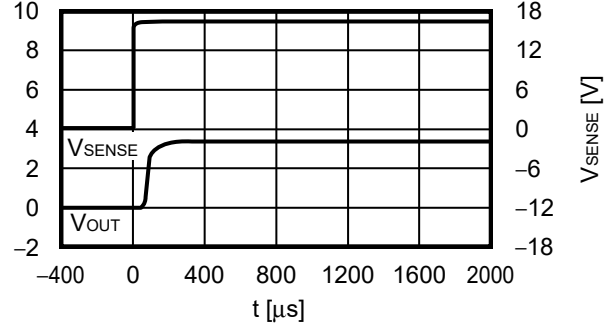
3.1 V_{OUT} = 1.8 V

V_{IN} = 4.0 V, C_{IN} = C_L = 1.0 μF, I_{OUT} = 20 mA, V_{SENSE} = 0 V ↔ 16 V



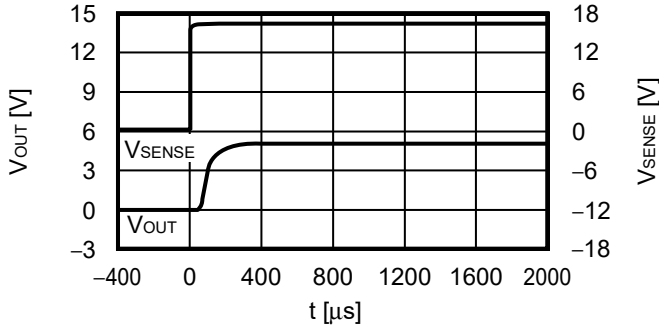
3.2 V_{OUT} = 3.3 V

V_{IN} = 5.3 V, C_{IN} = C_L = 1.0 μF, I_{OUT} = 20 mA, V_{SENSE} = 0 V ↔ 16 V



3.3 V_{OUT} = 5.0 V

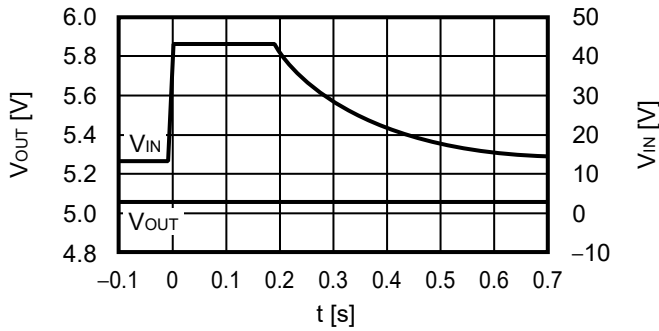
V_{IN} = 7.0 V, C_{IN} = C_L = 1.0 μF, I_{OUT} = 20 mA, V_{SENSE} = 0 V ↔ 16 V



4. Load dump characteristics (Ta = +25°C)

4.1 V_{OUT} = 5.0 V

I_{OUT} = 0.1 mA, V_{IN} = 13.5 V ↔ 45.0 V, C_{IN} = C_L = 1.0 μF



5. Output capacitance vs. Discharge time characteristics (Ta = +25°C)

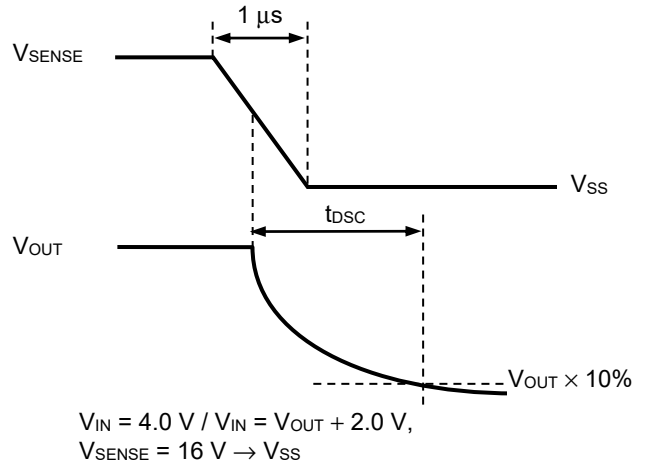
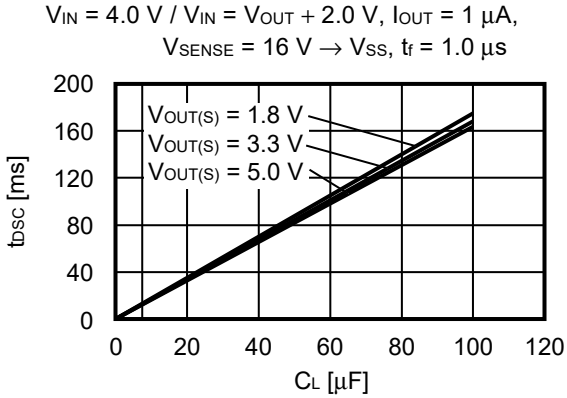


Figure 28 Test conditions of discharge time

6. Example of equivalent series resistance vs. Output current characteristics (Ta = +25°C)

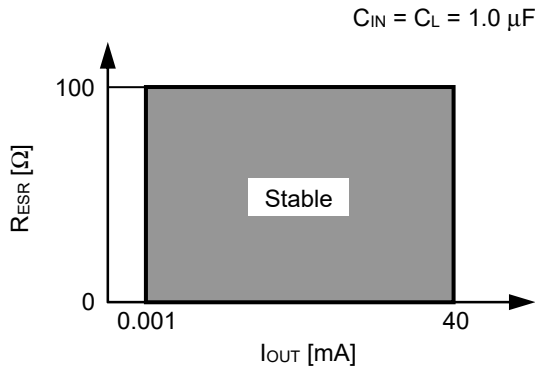
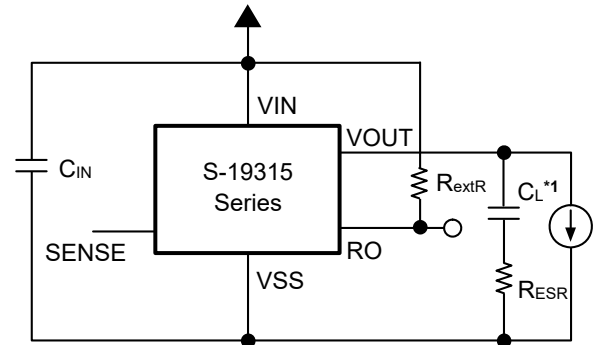


Figure 29

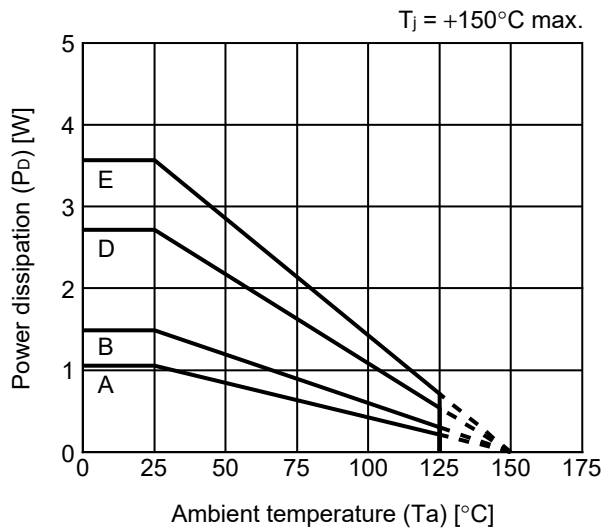


*1. C_L : TDK Corporation CGA4J3X8R1C105K (1.0 μF)

Figure 30

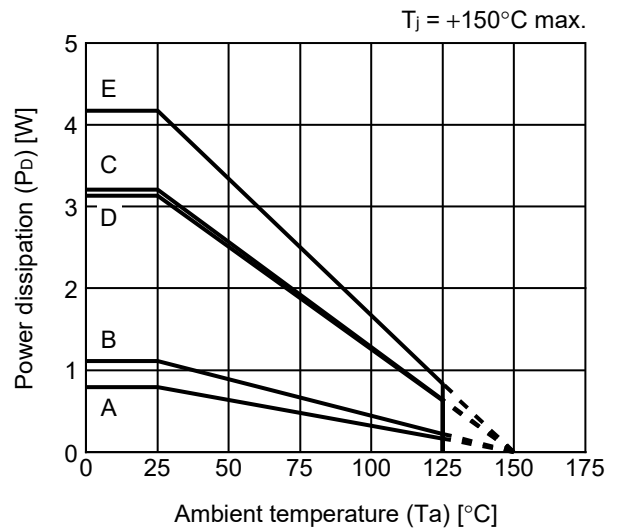
■ Power Dissipation

SOT-89-5



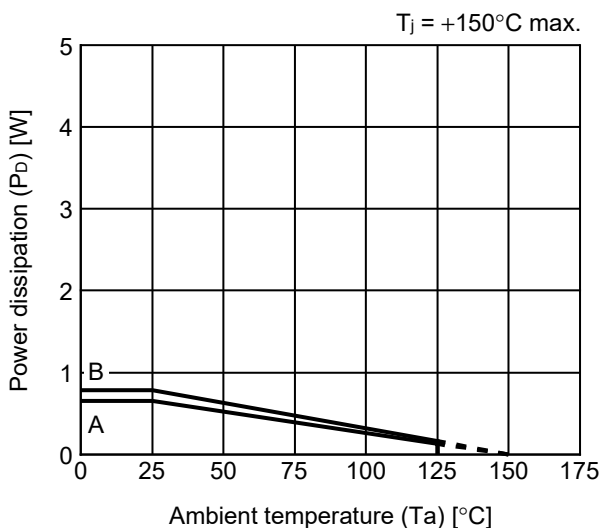
Board	Power Dissipation (P_D)
A	1.05 W
B	1.49 W
C	–
D	2.72 W
E	3.57 W

HTMSOP-8




Board	Power Dissipation (P_D)
A	0.79 W
B	1.11 W
C	3.21 W
D	3.13 W
E	4.17 W

SOT-23-5

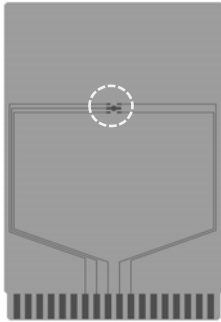


Board	Power Dissipation (P_D)
A	0.65 W
B	0.78 W
C	–
D	–
E	–

SOT-89-5 Test Board

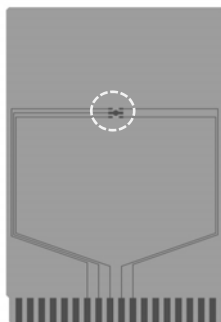
 IC Mount Area

(1) Board A



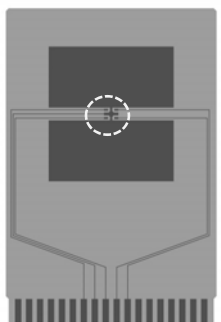
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



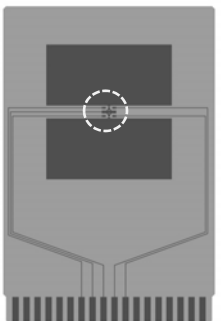
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

(3) Board D



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm ² t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

(4) Board E




Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm ² t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm



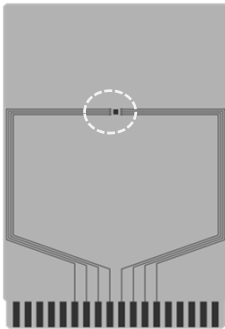
enlarged view

No. SOT895-A-Board-SD-1.0

HTMSOP-8 Test Board

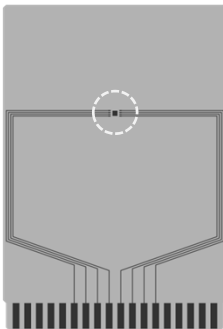
 IC Mount Area

(1) Board A



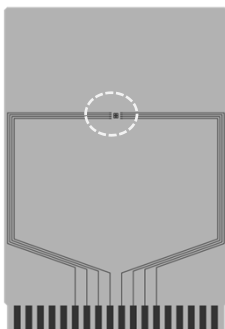
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

(3) Board C



Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		Number: 4 Diameter: 0.3 mm



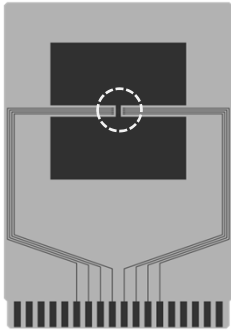
enlarged view

No. HTMSOP8-A-Board-SD-1.0

HTMSOP-8 Test Board

 IC Mount Area

(4) Board D

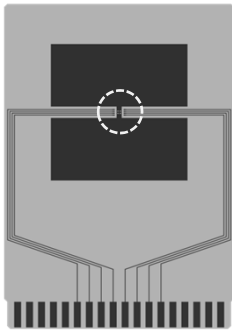


Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	4	
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm ² t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via	-	



enlarged view

(5) Board E



Item	Specification	
Size [mm]	114.3 x 76.2 x t1.6	
Material	FR-4	
Number of copper foil layer	4	
Copper foil layer [mm]	1	Pattern for heat radiation: 2000mm ² t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via	Number: 4 Diameter: 0.3 mm	



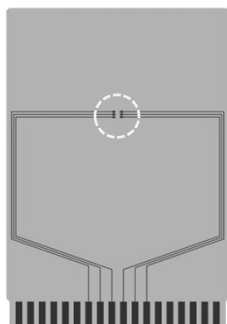
enlarged view

No. HTMSOP8-A-Board-SD-1.0

SOT-23-3/3S/5/6 Test Board

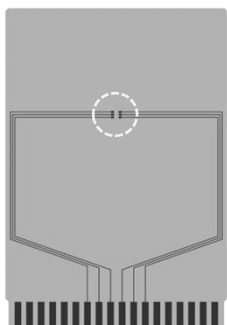
 IC Mount Area

(1) Board A



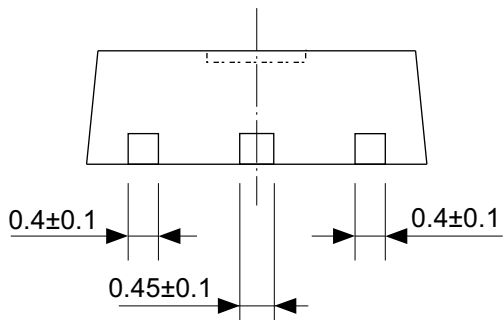
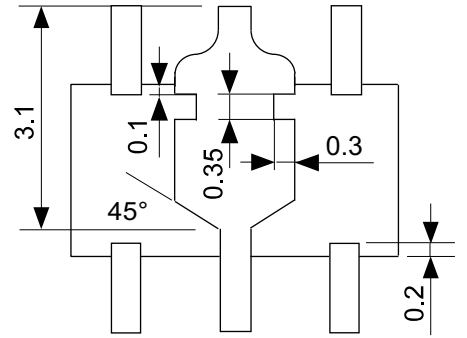
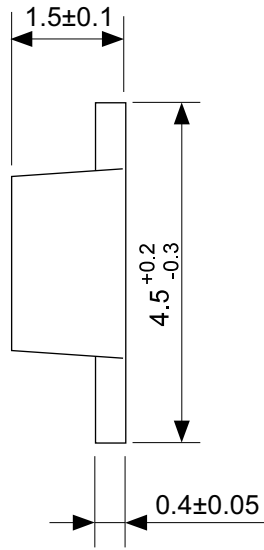
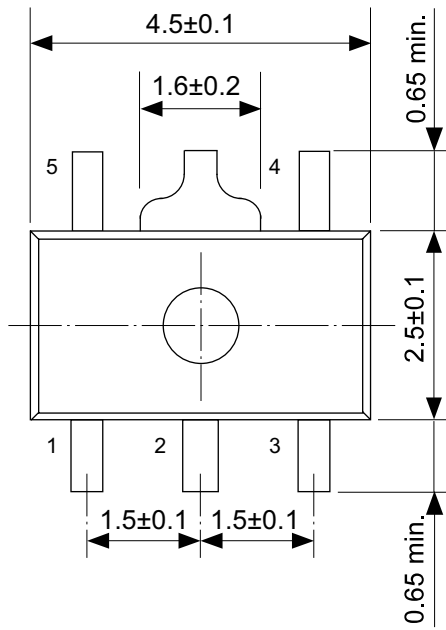
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		2
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	-
	3	-
	4	74.2 x 74.2 x t0.070
Thermal via		-

(2) Board B



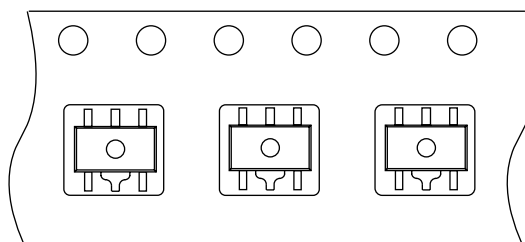
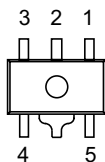
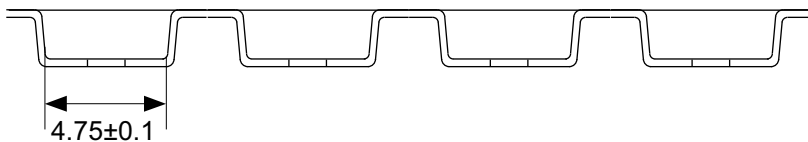
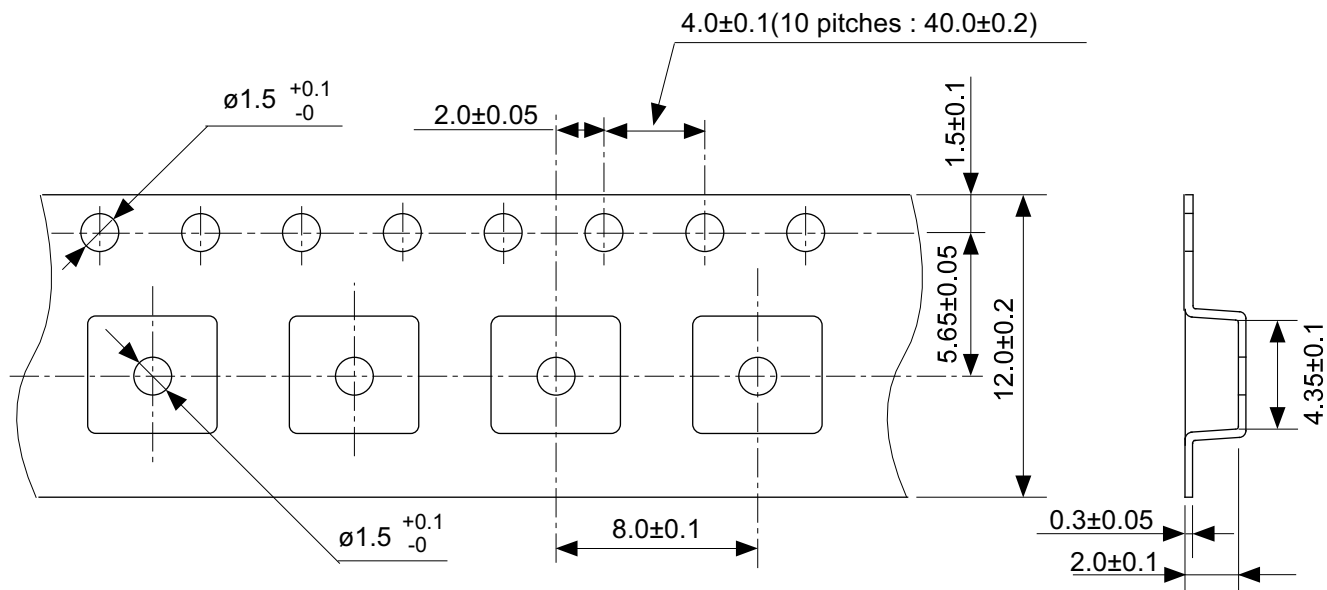
Item		Specification
Size [mm]		114.3 x 76.2 x t1.6
Material		FR-4
Number of copper foil layer		4
Copper foil layer [mm]	1	Land pattern and wiring for testing: t0.070
	2	74.2 x 74.2 x t0.035
	3	74.2 x 74.2 x t0.035
	4	74.2 x 74.2 x t0.070
Thermal via		-

No. SOT23x-A-Board-SD-2.0



No. UP005-A-P-SD-2.0

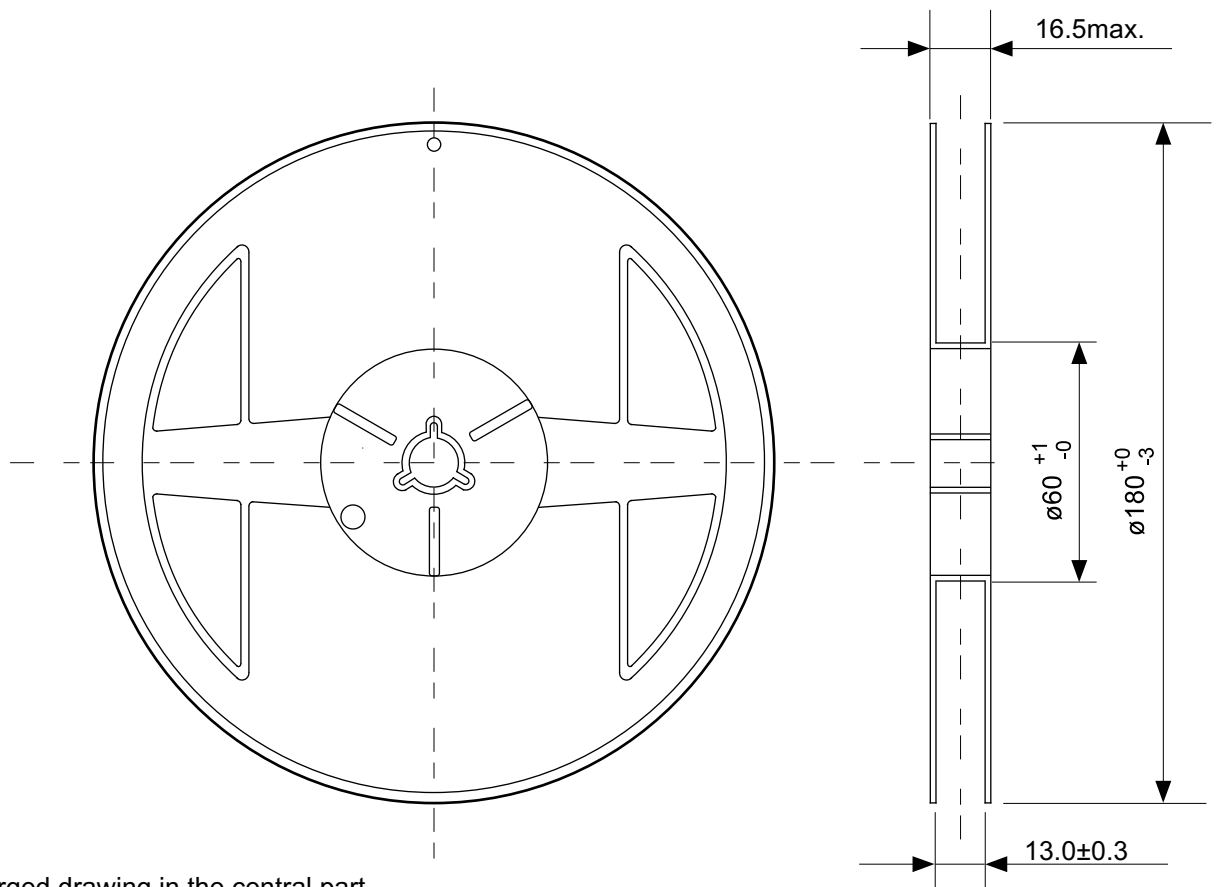
TITLE	SOT895-A-PKG Dimensions
No.	UP005-A-P-SD-2.0
ANGLE	
UNIT	mm
ABLIC Inc.	



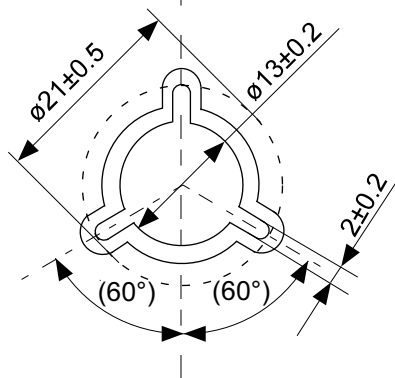
→
Feed direction

No. UP005-A-C-SD-2.0

TITLE	SOT895-A-Carrier Tape
No.	UP005-A-C-SD-2.0
ANGLE	
UNIT	mm
ABLIC Inc.	

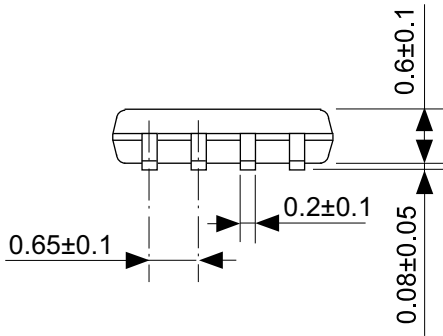
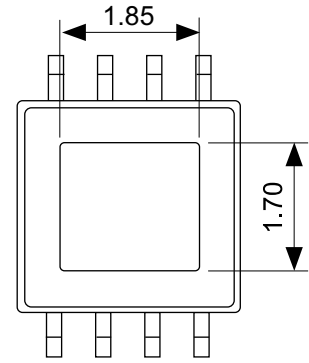
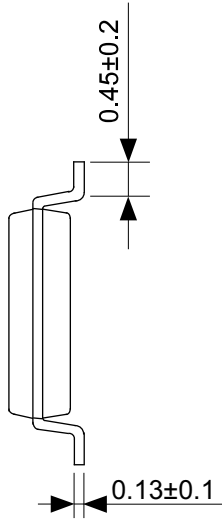
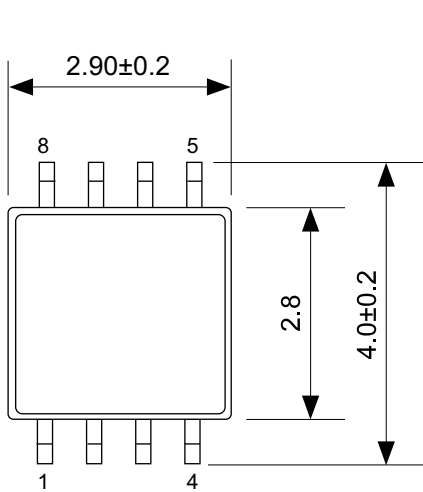


Enlarged drawing in the central part



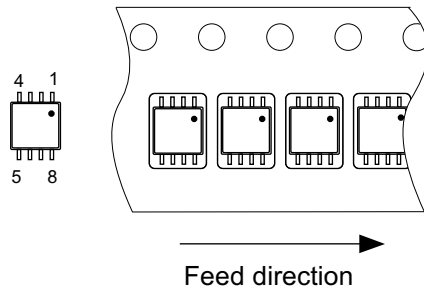
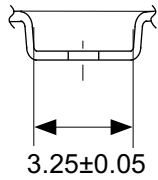
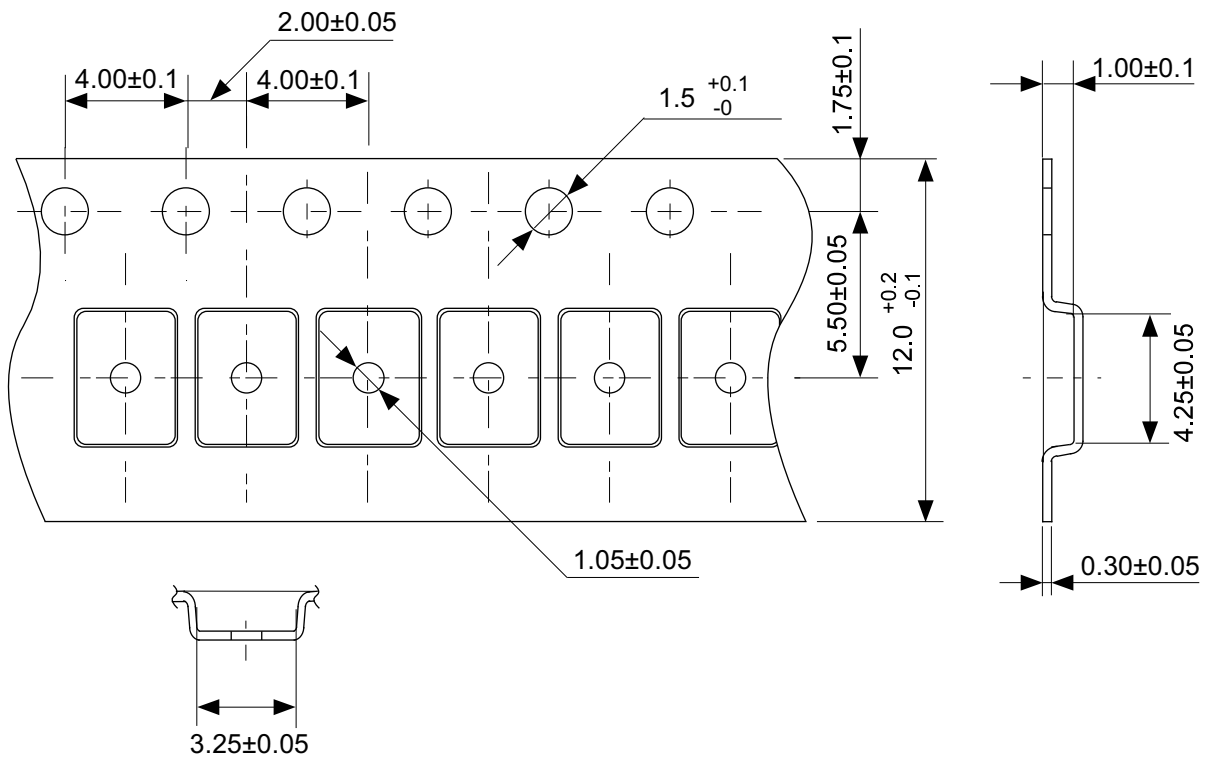
No. UP005-A-R-SD-1.1

TITLE	SOT895-A-Reel		
No.	UP005-A-R-SD-1.1		
ANGLE		QTY.	1,000
UNIT	mm		
ABLIC Inc.			



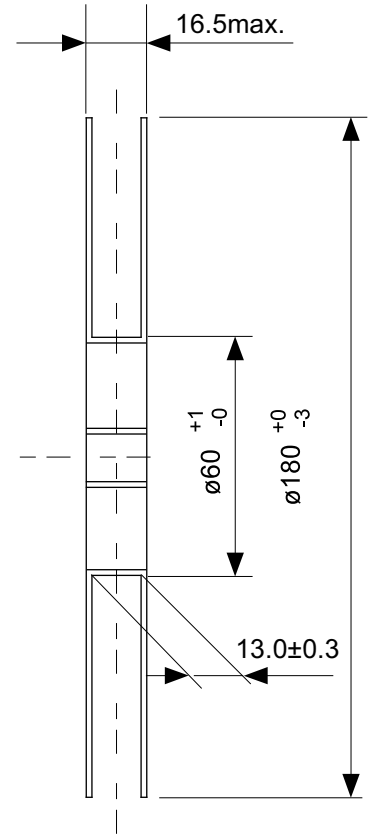
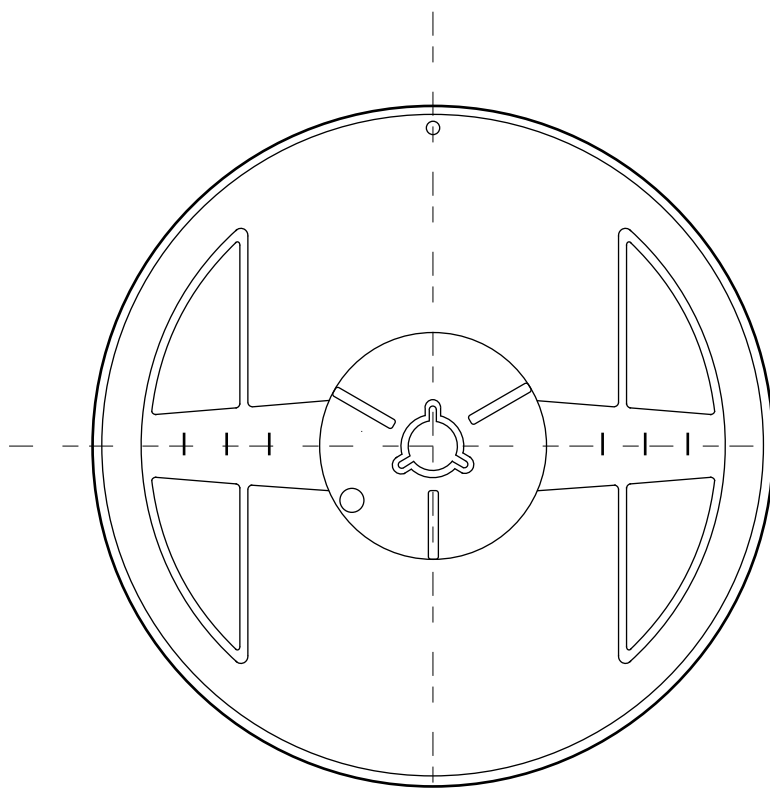
No. FP008-A-P-SD-2.0

TITLE	HTMSOP8-A-PKG Dimensions
No.	FP008-A-P-SD-2.0
ANGLE	
UNIT	mm
ABLIC Inc.	

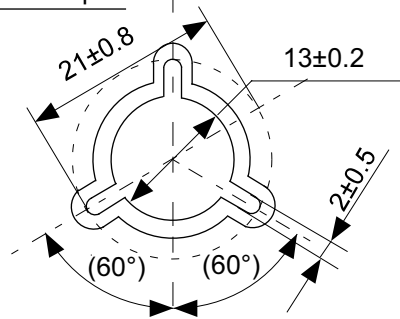


No. FP008-A-C-SD-1.0

TITLE	HTMSOP8-A-Carrier Tape
No.	FP008-A-C-SD-1.0
ANGLE	
UNIT	mm
ABLIC Inc.	

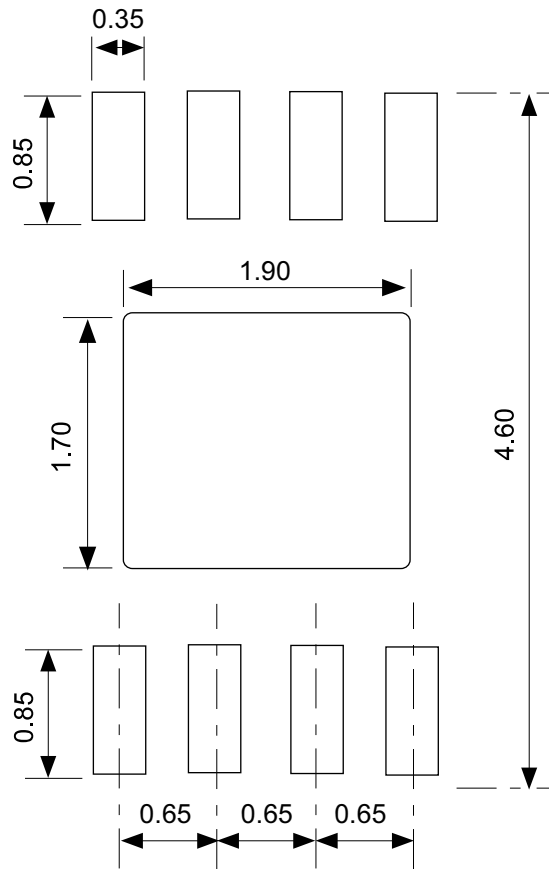


Enlarged drawing in the central part



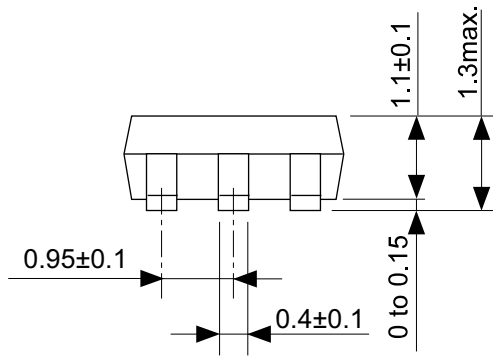
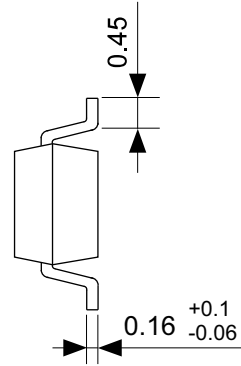
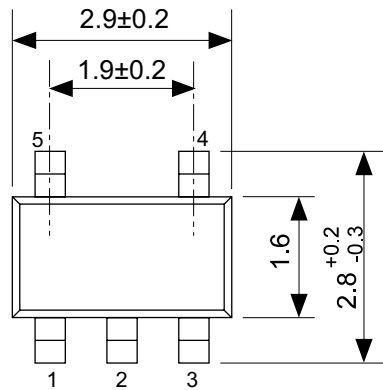
No. FP008-A-R-SD-1.0

TITLE	HTMSOP8-A-Reel		
No.	FP008-A-R-SD-1.0		
ANGLE		QTY.	4,000
UNIT	mm		
ABLIC Inc.			



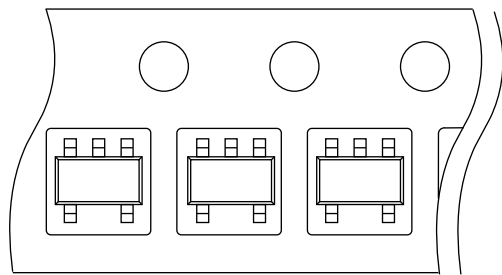
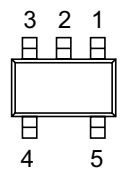
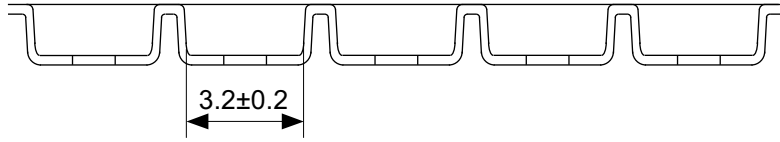
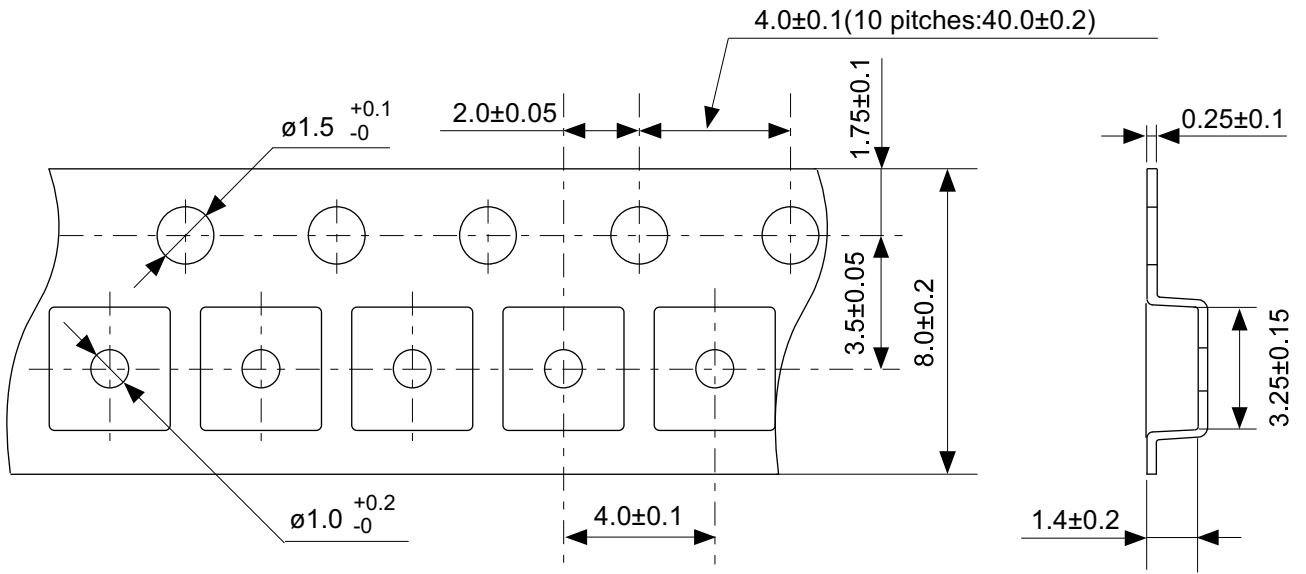
No. FP008-A-L-SD-2.0

TITLE	HTMSOP8-A -Land Recommendation
No.	FP008-A-L-SD-2.0
ANGLE	
UNIT	mm
ABLIC Inc.	



No. MP005-A-P-SD-1.3

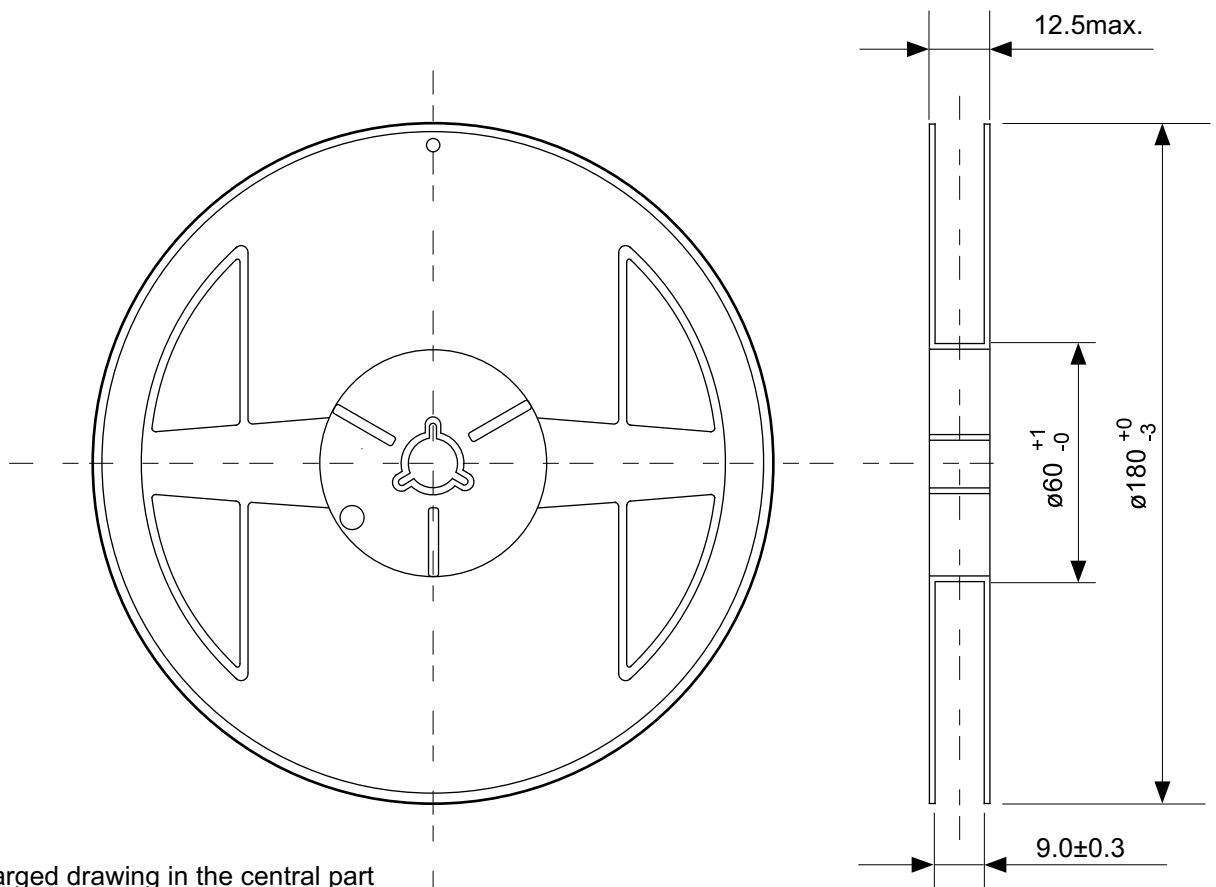
TITLE	SOT235-A-PKG Dimensions
No.	MP005-A-P-SD-1.3
ANGLE	
UNIT	mm
ABLIC Inc.	



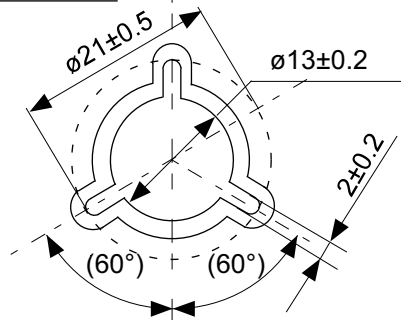
Feed direction →

No. MP005-A-C-SD-2.1

TITLE	SOT235-A-Carrier Tape
No.	MP005-A-C-SD-2.1
ANGLE	
UNIT	mm
ABLIC Inc.	



Enlarged drawing in the central part



No. MP005-A-R-SD-1.1

TITLE	SOT235-A-Reel		
No.	MP005-A-R-SD-1.1		
ANGLE		QTY.	3,000
UNIT	mm		
ABLIC Inc.			

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2.4-2019.07